

ESE370: Circuit-Level Modeling, Design, and Optimization for Digital Systems

Lec 31: November 24, 2021
Crosstalk

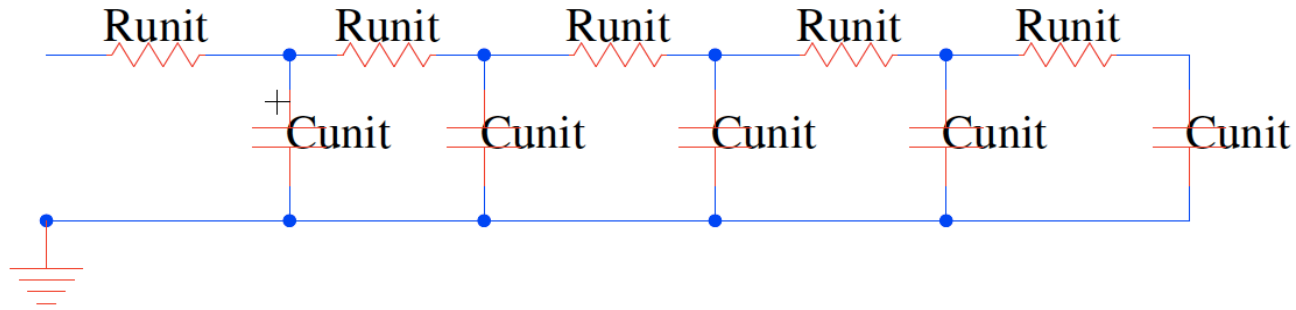


Today

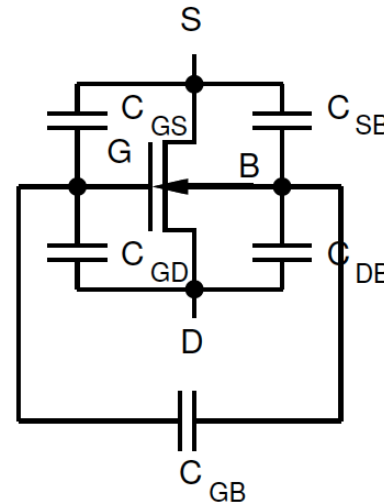
- Crosstalk
 - Characterization
 - Magnitude
 - Avoiding
 - Design practices

Capacitance

- There are capacitors everywhere
- Already talked about
 - Wires modeled as a distributed RC network



- Parasitic capacitances between terminals on transistor





Capacitance Everywhere

- Potentially a capacitor between any two conductors
 - On the chip
 - On the package
 - On the board
- All wires
 - Package pins
 - PCB traces
 - Cable wires
 - Bit/word lines



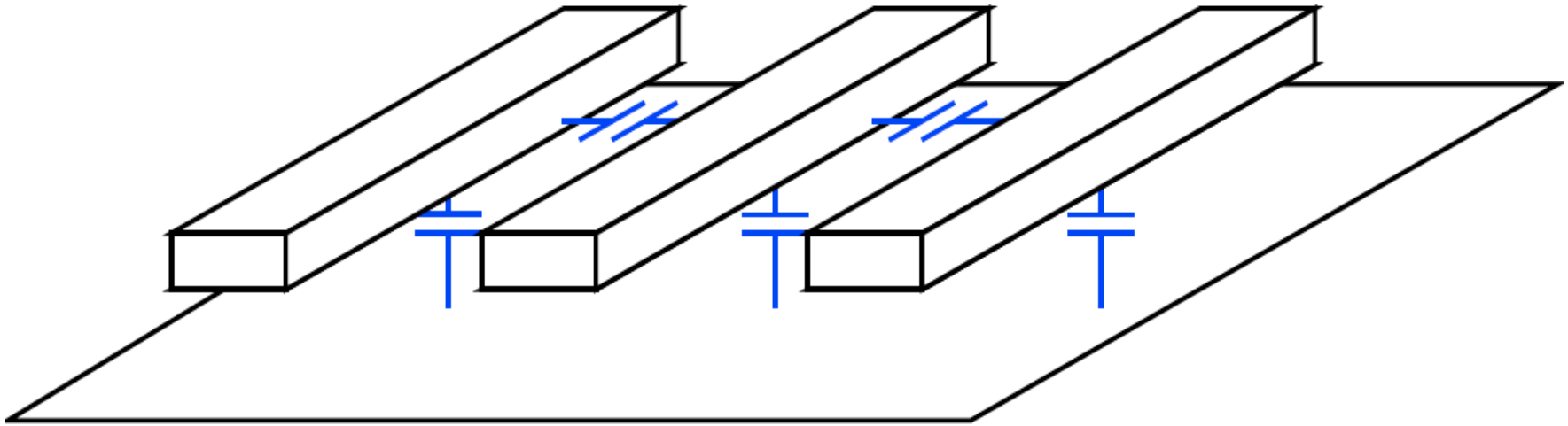
Capacitance...

- ❑ ...decreases with conductor separation
- ❑ ...increases with size
- ❑ ...depends on dielectric

$$C = \epsilon_r \epsilon_0 \frac{A}{d}$$

Wire Capacitance

- ❑ Changes in voltage on one wire may couple through parasitic capacitance to an adjacent wire





Crosstalk

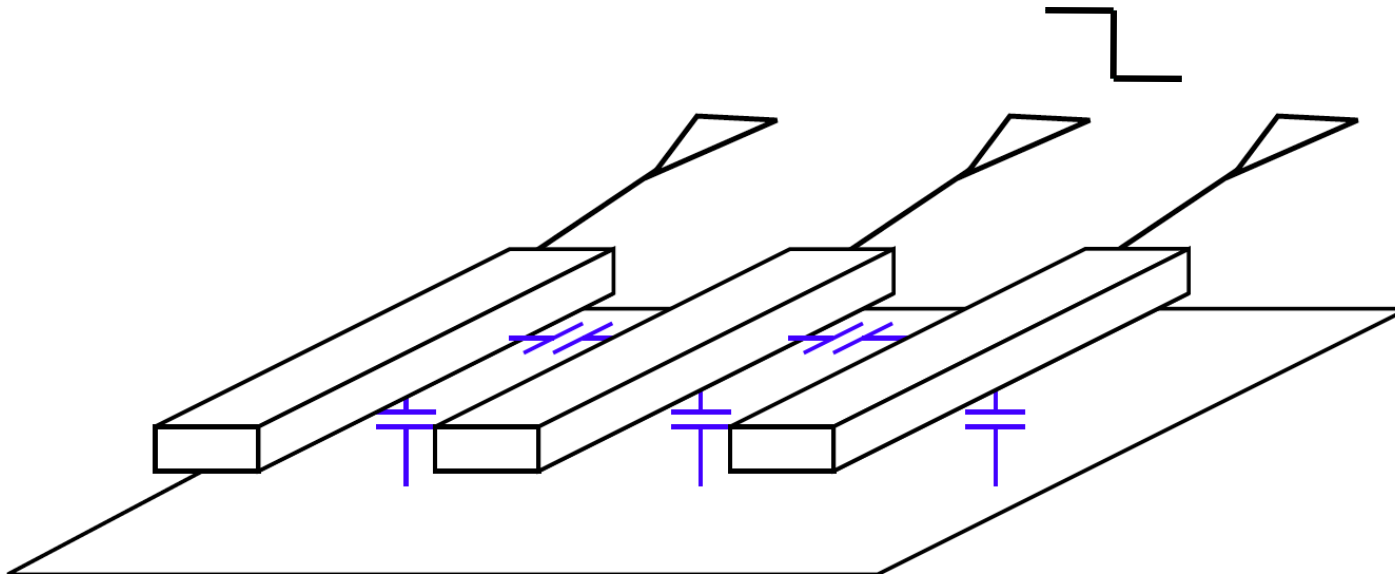
- ❑ A capacitor does not like to change its voltage instantaneously
- ❑ A wire has high capacitance to its neighbor.
 - When the neighbor switches from 1- \rightarrow 0 or 0- \rightarrow 1, the wire tends to switch too.
 - Called capacitive *coupling* or *crosstalk*.
- ❑ Crosstalk effects
 - Noise on non-switching wires
 - Increased delay on switching wires

Qualitative



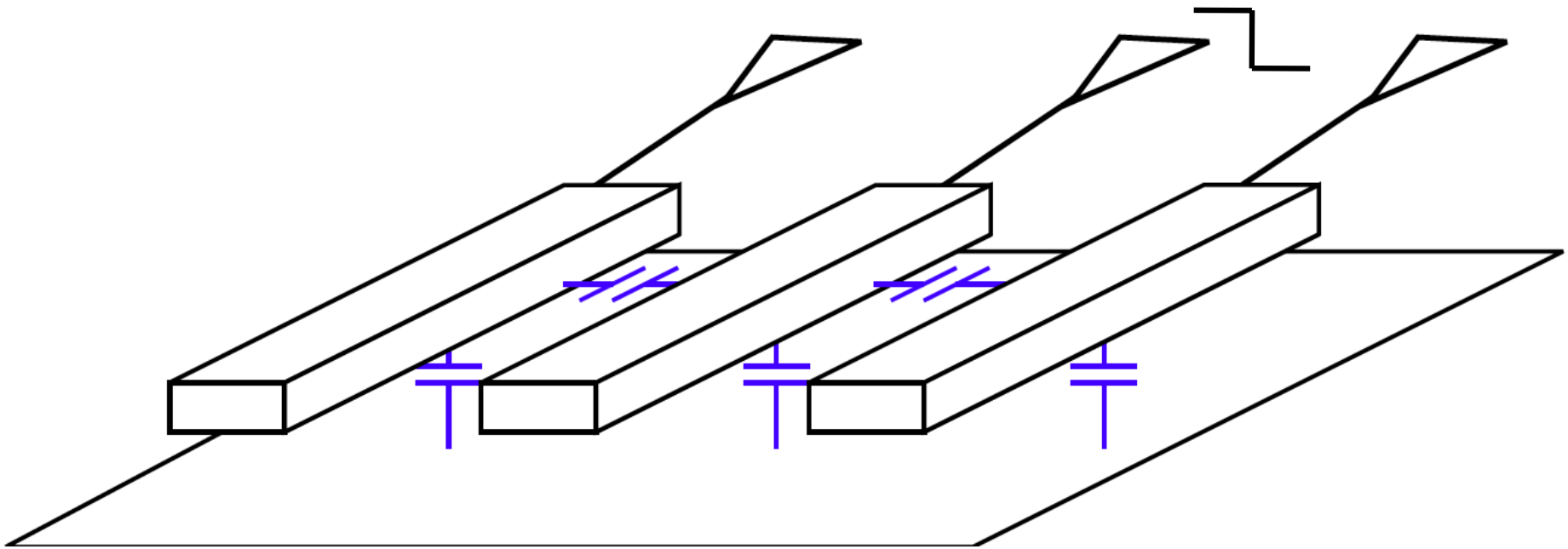
Undriven Wire

- ❑ What happens to undriven wire?
- ❑ Where do we have undriven wires?



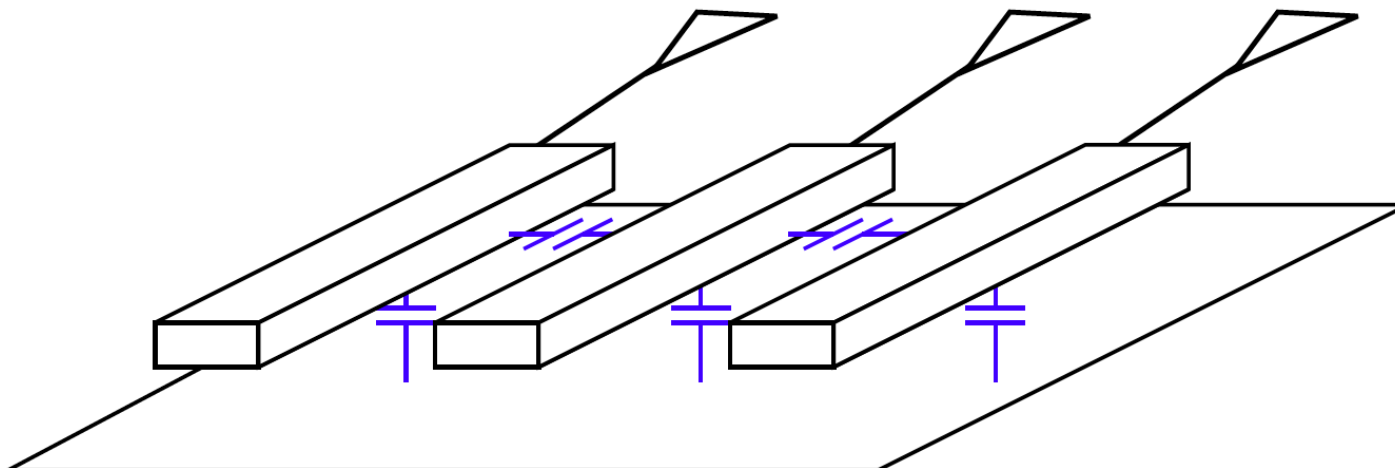
Driven Wire

- What happens to a driven “neighbor” wire?
 - One wire switches
 - Neighbors driven but not switch
 - What happens to neighbors?



Driven Wire

- ❑ Can this be a problem?
- ❑ What if switching neighbor is:
 - Clock line
 - Non-clock signal used in synchronous system
 - Asynchronous control





Clocked Logic

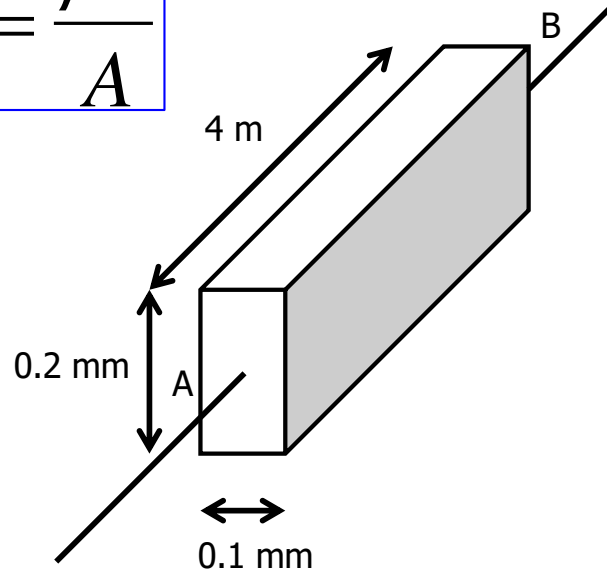
- ❑ CMOS driven lines
- ❑ Clocked logic
 - Willing to wait to settle/evaluate
- ❑ Impact is on delay
 - May increase delay of transitions

Quantitative

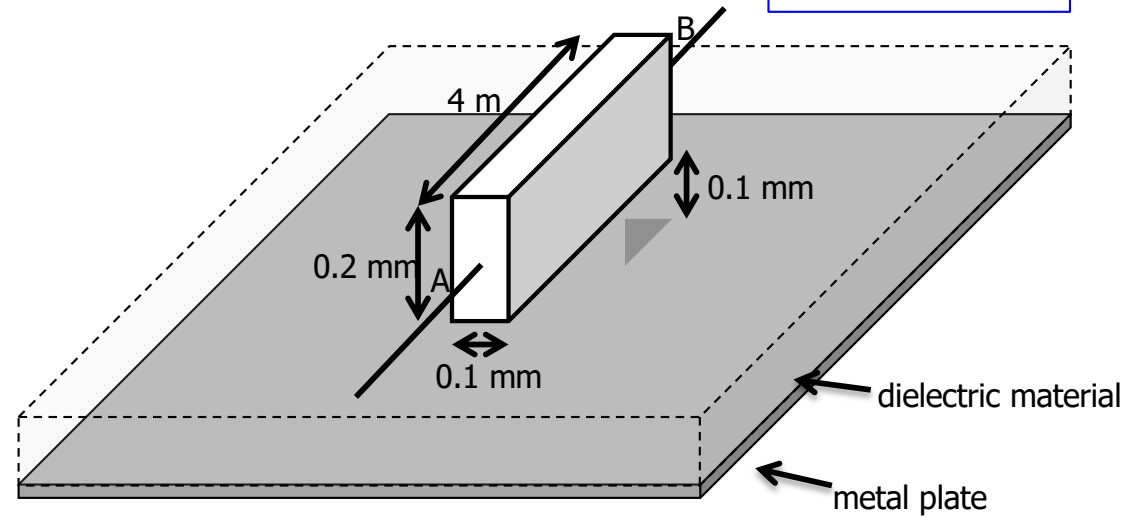


Isolated Wire RC

$$R = \frac{\rho L}{A}$$

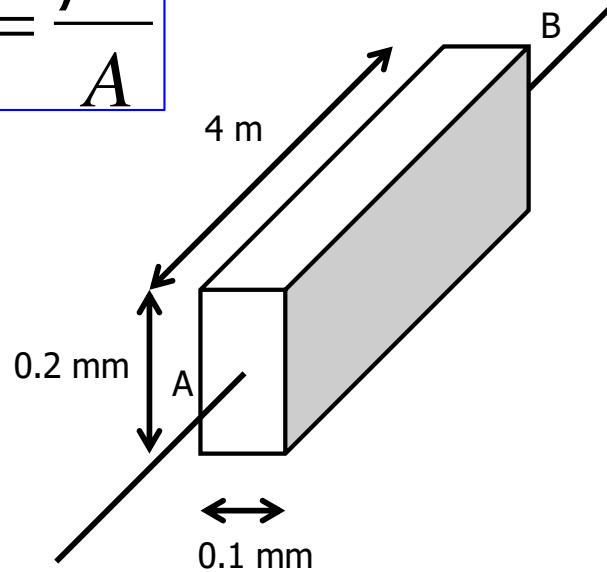


$$C = \epsilon_d \frac{A}{d}$$

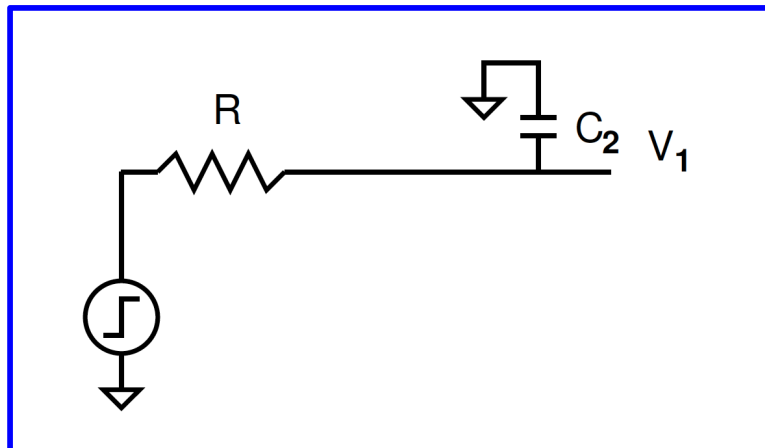
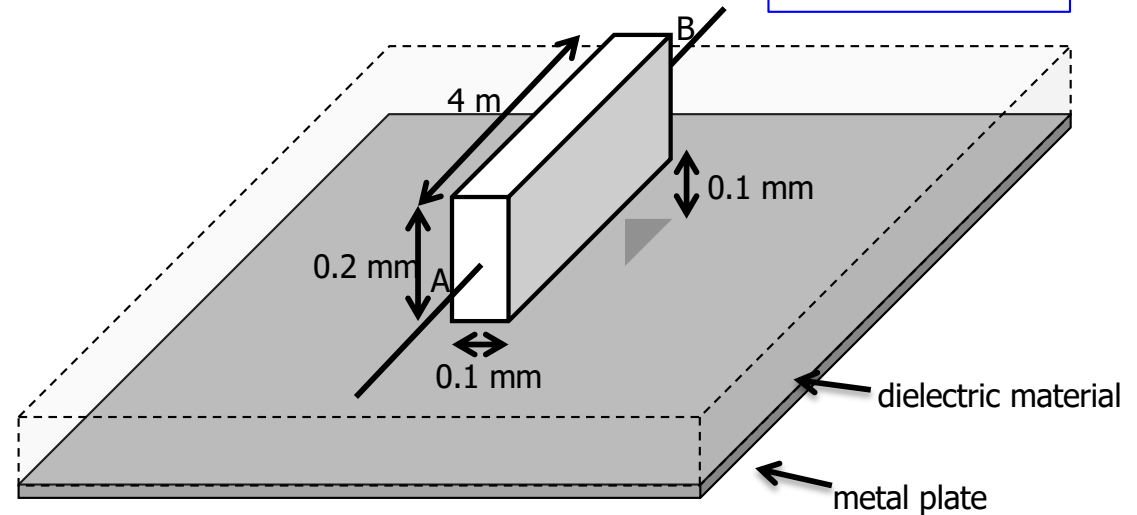


Isolated Wire RC

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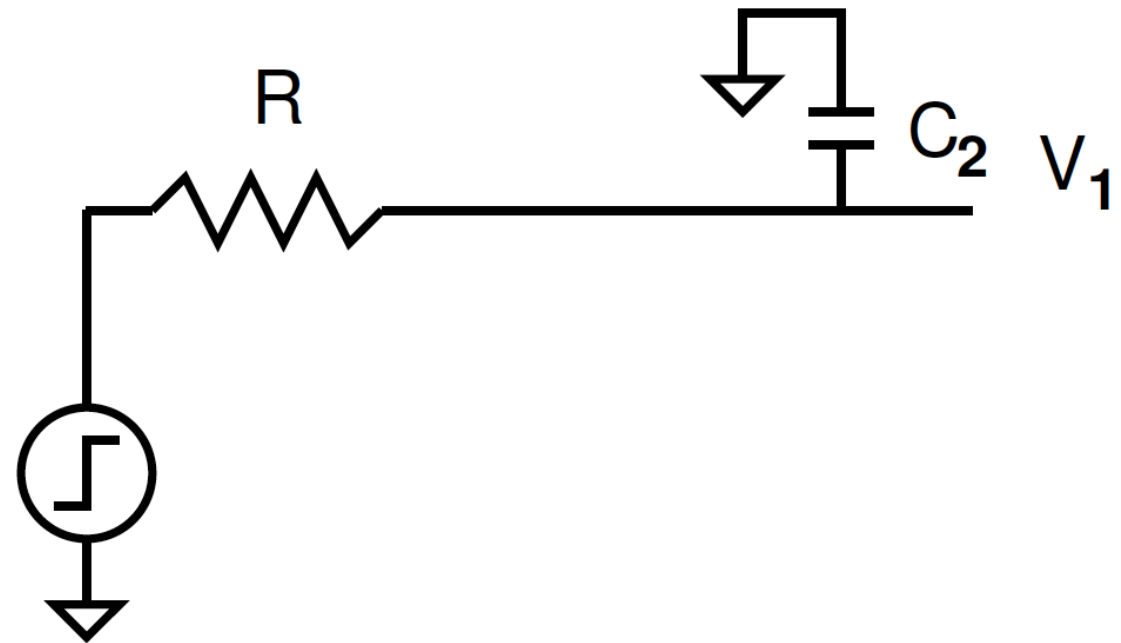


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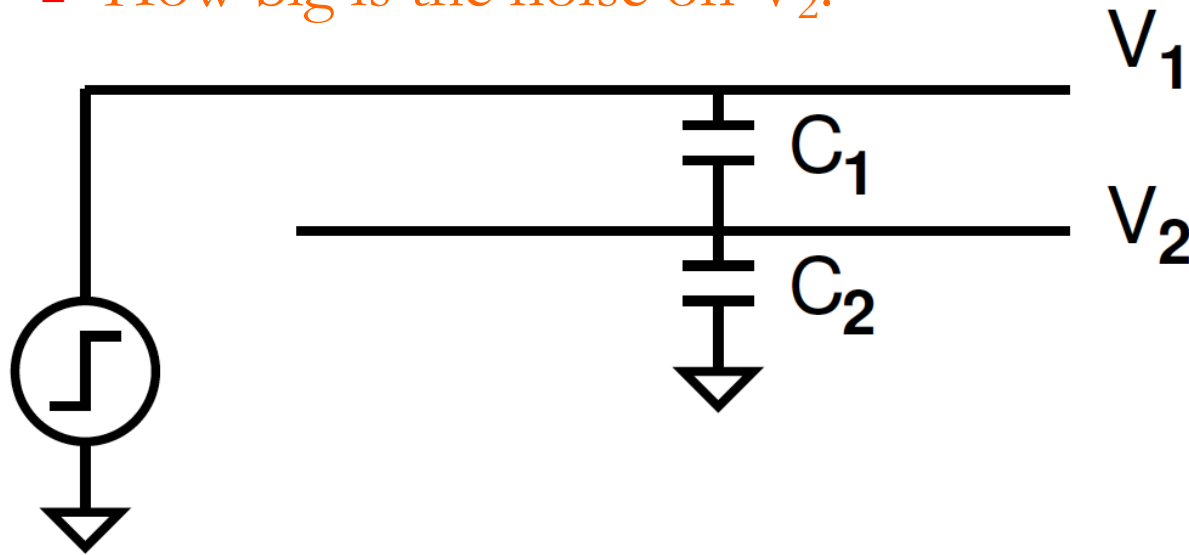
Wire step response (preclass 1)

- Step response for isolated wire?



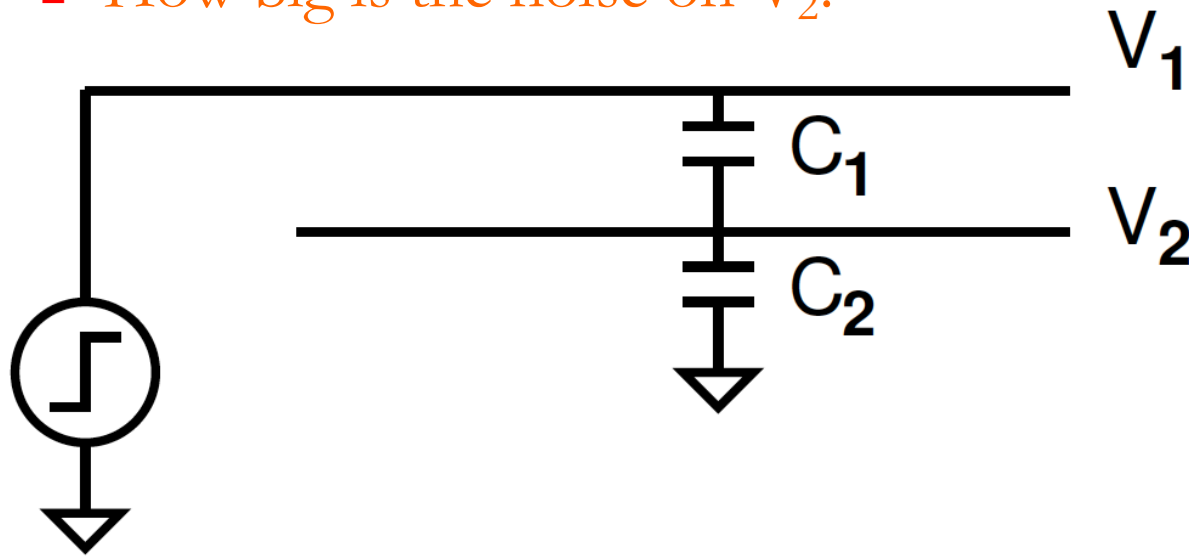
Undriven Adjacent Wire (preclass 2)

- V_1 transitions from 0 to V
 - How big is the noise on V_2 ?



Undriven Adjacent Wire

- V_1 transitions from 0 to V
 - How big is the noise on V_2 ?

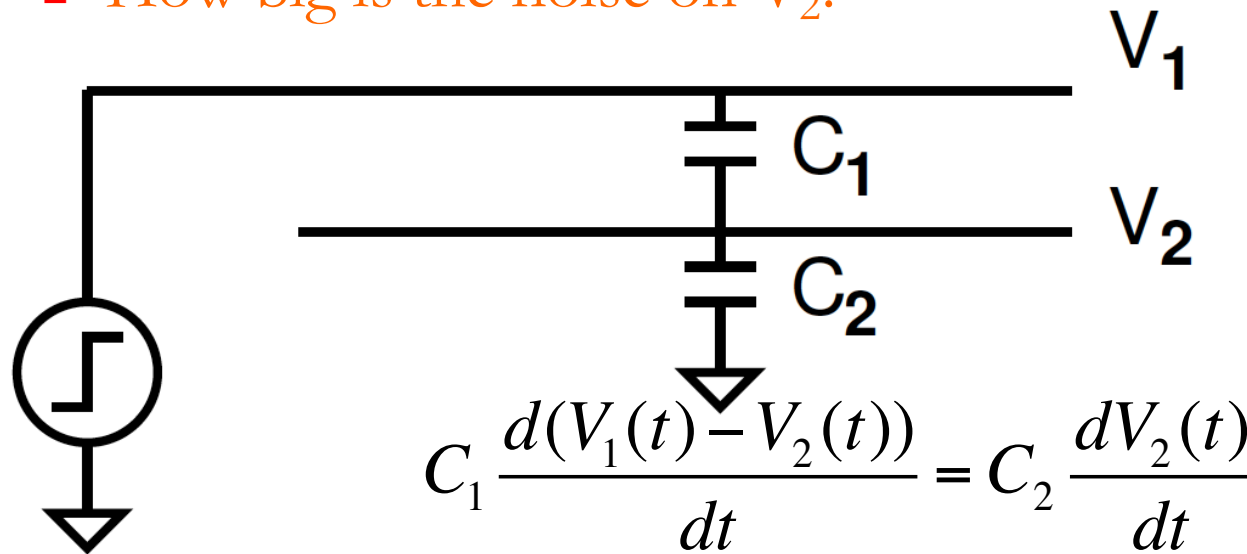


$$I(t) = C \frac{dV(t)}{dt}$$

Undriven Adjacent Wire

□ V_1 transitions from 0 to V

■ How big is the noise on V_2 ?



$$I(t) = C \frac{dV(t)}{dt}$$

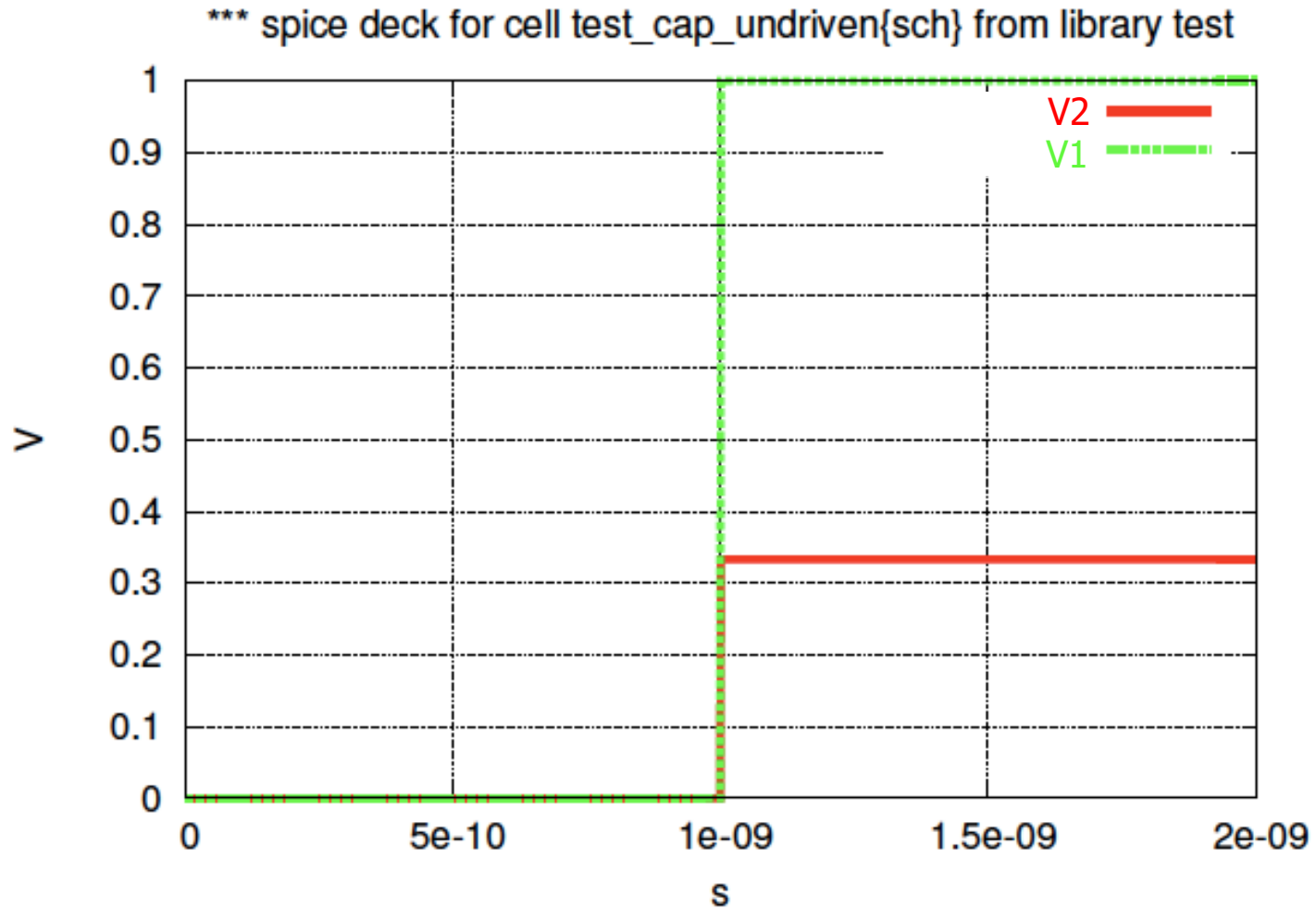
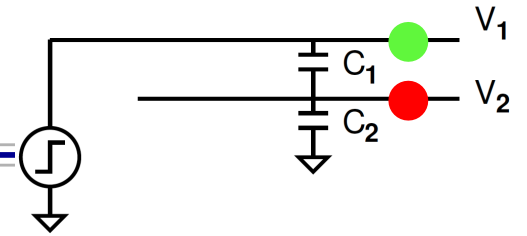
$$C_1 \frac{d(V_1(t) - V_2(t))}{dt} = C_2 \frac{dV_2(t)}{dt}$$

$$C_1 \frac{dV_1(t)}{dt} = (C_1 + C_2) \frac{dV_2(t)}{dt}$$

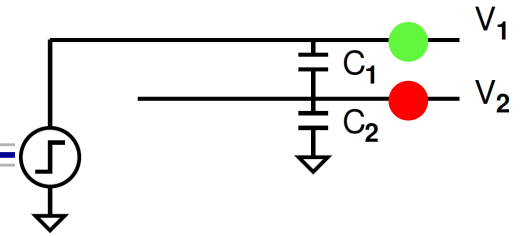
$$C_1 V_1(t) = (C_1 + C_2) V_2(t)$$

$$V_2(t) = \frac{C_1}{C_1 + C_2} V_1(t)$$

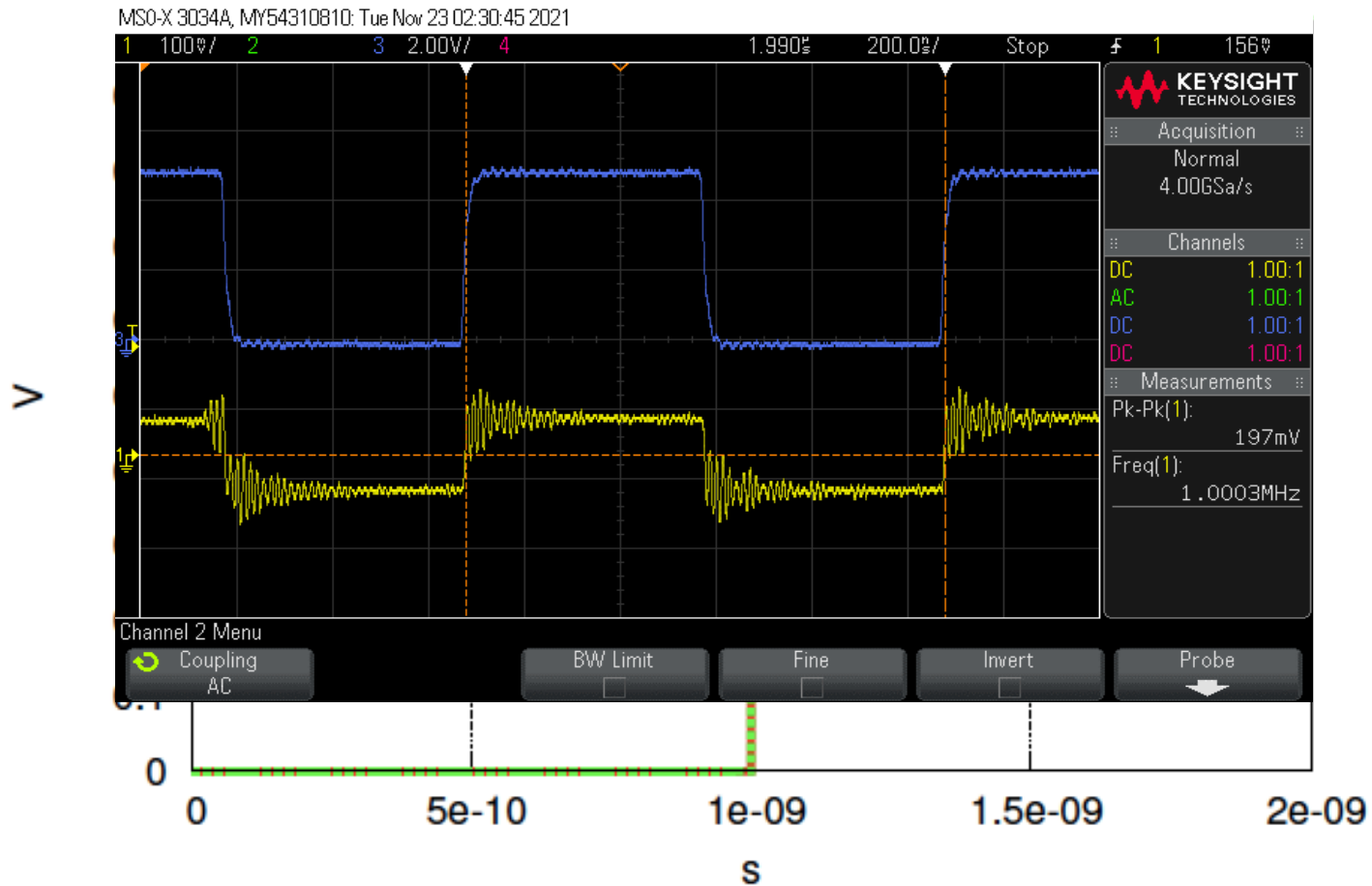
SPICE $C_1=10\text{pF}$, $C_2=20\text{pF}$



SPICE $C_1=10\text{pF}$, $C_2=20\text{pF}$

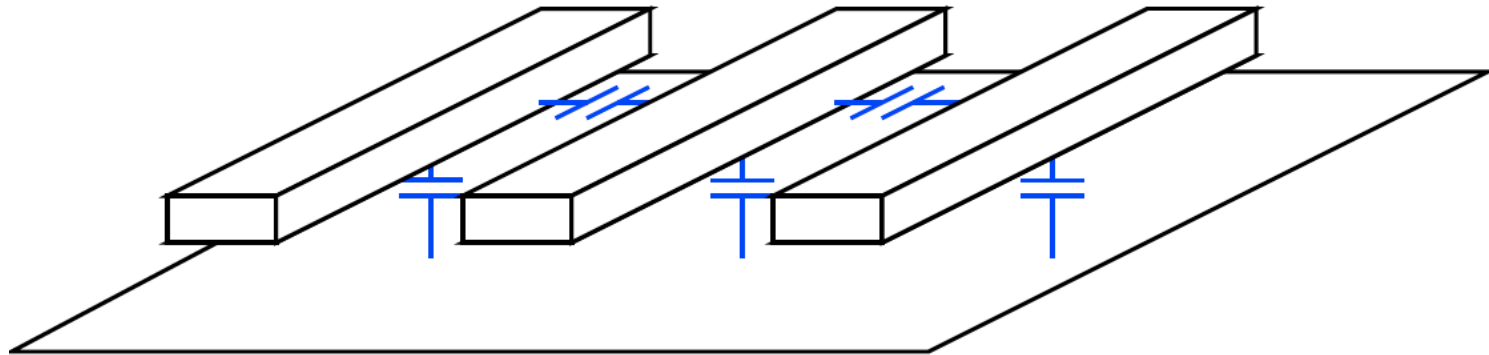


*** spice deck for cell test_cap_undriven{sch} from library test



Good (?) Capacitance

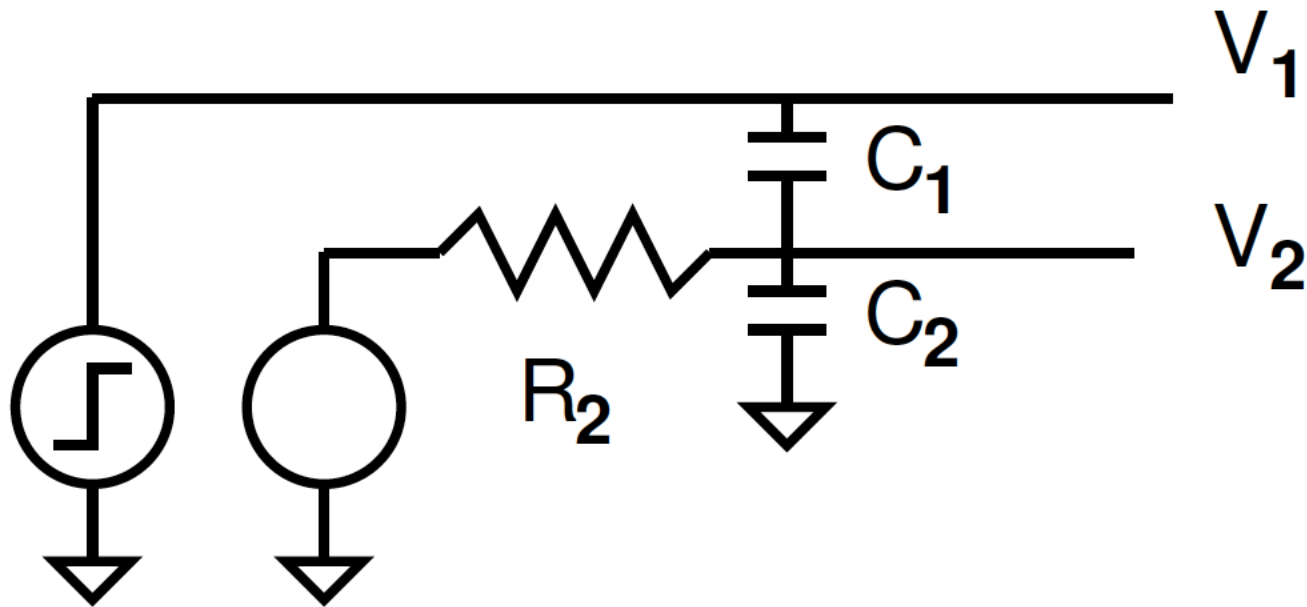
- High capacitance to ground plane (C_2)
 - Limits node swing from adjacent conductors



$$V_2 = \left(\frac{C_1}{C_1 + C_2} \right) V_1$$

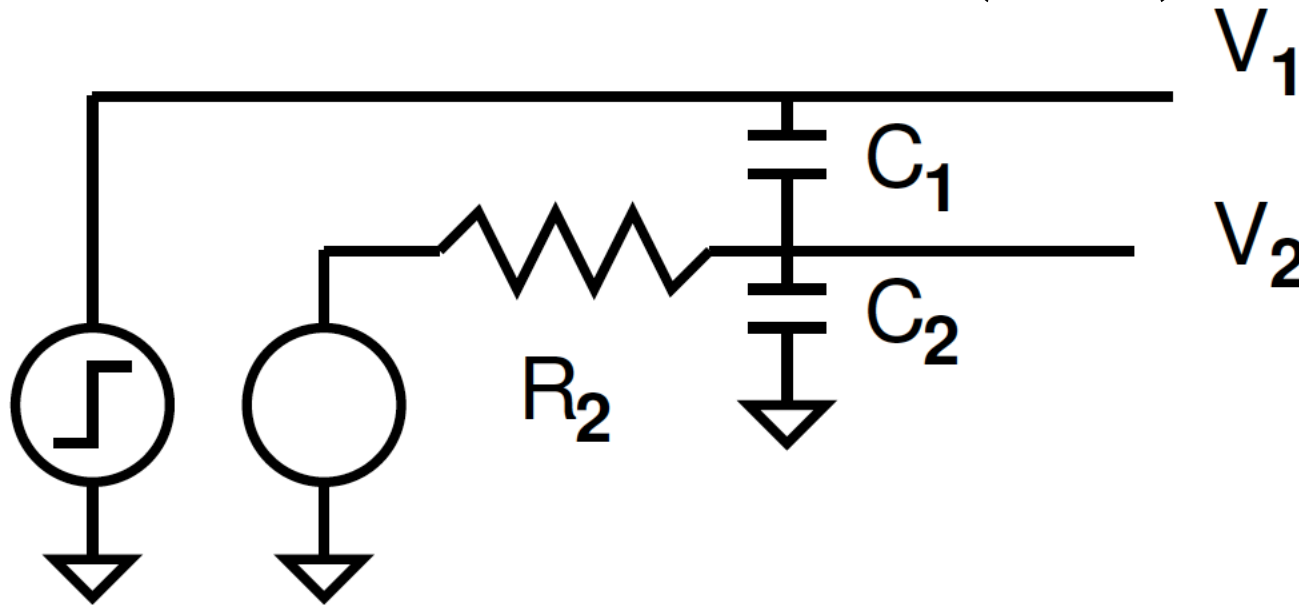
Driven Adjacent Wire (preclass 2)

- What happens when neighbor line is driven?

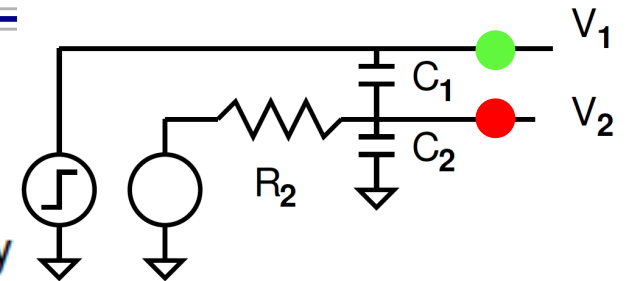


Driven Adjacent Wire

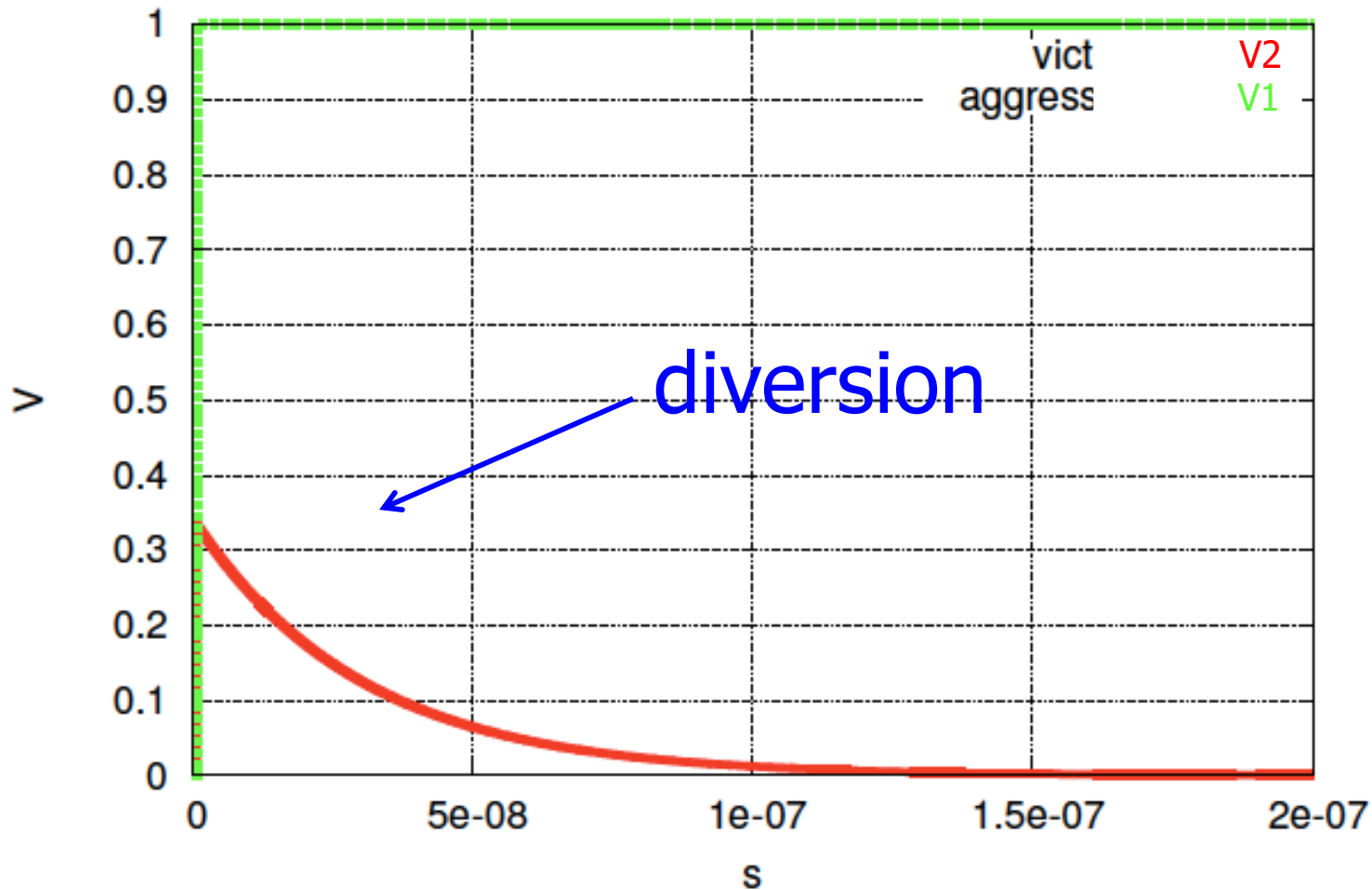
- What happens when neighbor line is driven?
 - Recovers with time constant: $R_2(C_1 + C_2)$



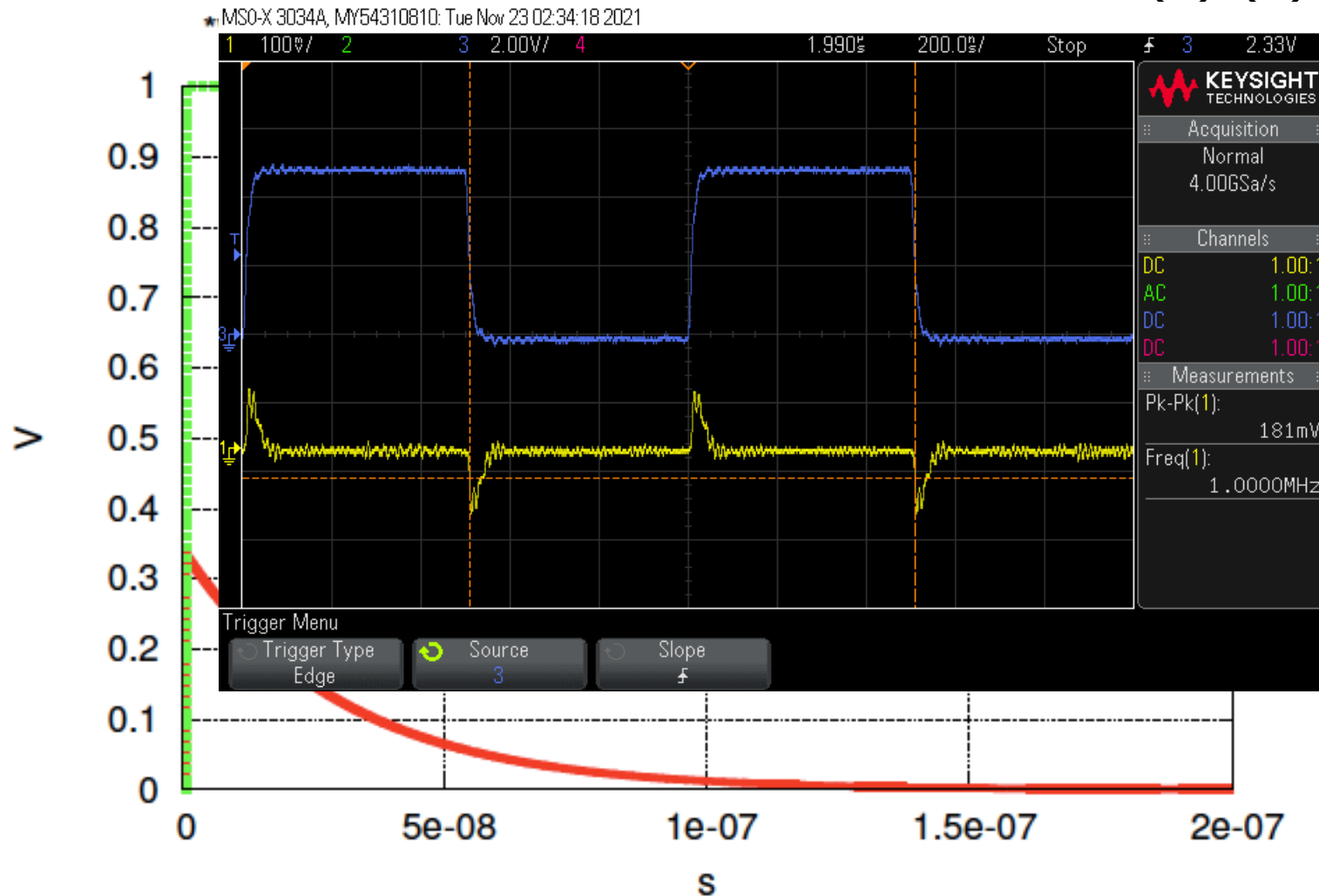
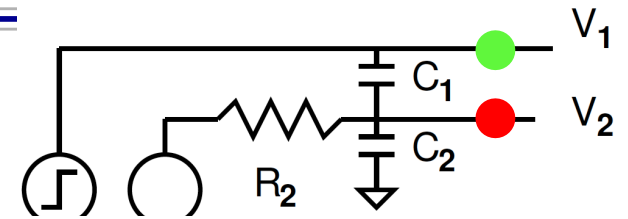
Spice: $R_2=1\text{K}$, $C_1=10\text{pF}$, $C_2=20\text{pF}$



*** spice deck for cell test_cap_undriven{sch} from library



Spice: $R_2=1\text{K}$, $C_1=10\text{pF}$, $C_2=20\text{pF}$



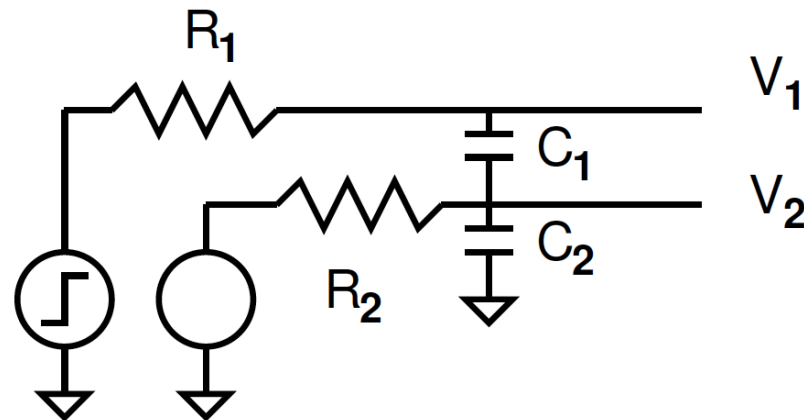
Magnitude of Noise on Driven Line (preclass 3)

□ Magnitude of diversion depends on relative time constants

■ $\tau_1 \ll \tau_2$

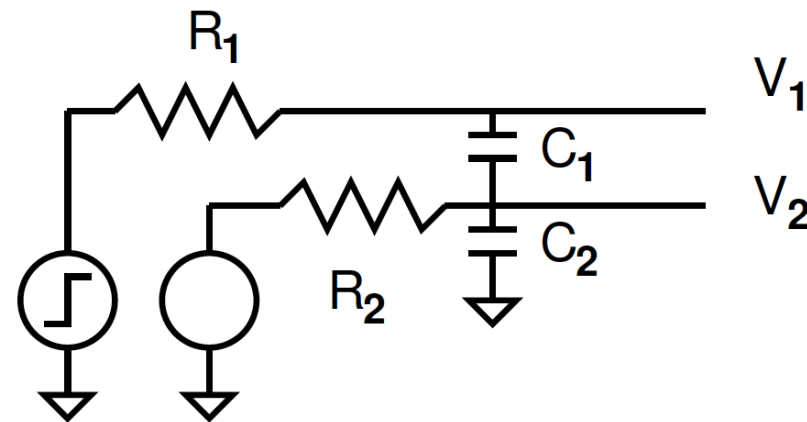
■ $\tau_1 \gg \tau_2$

■ $\tau_1 \sim \tau_2$



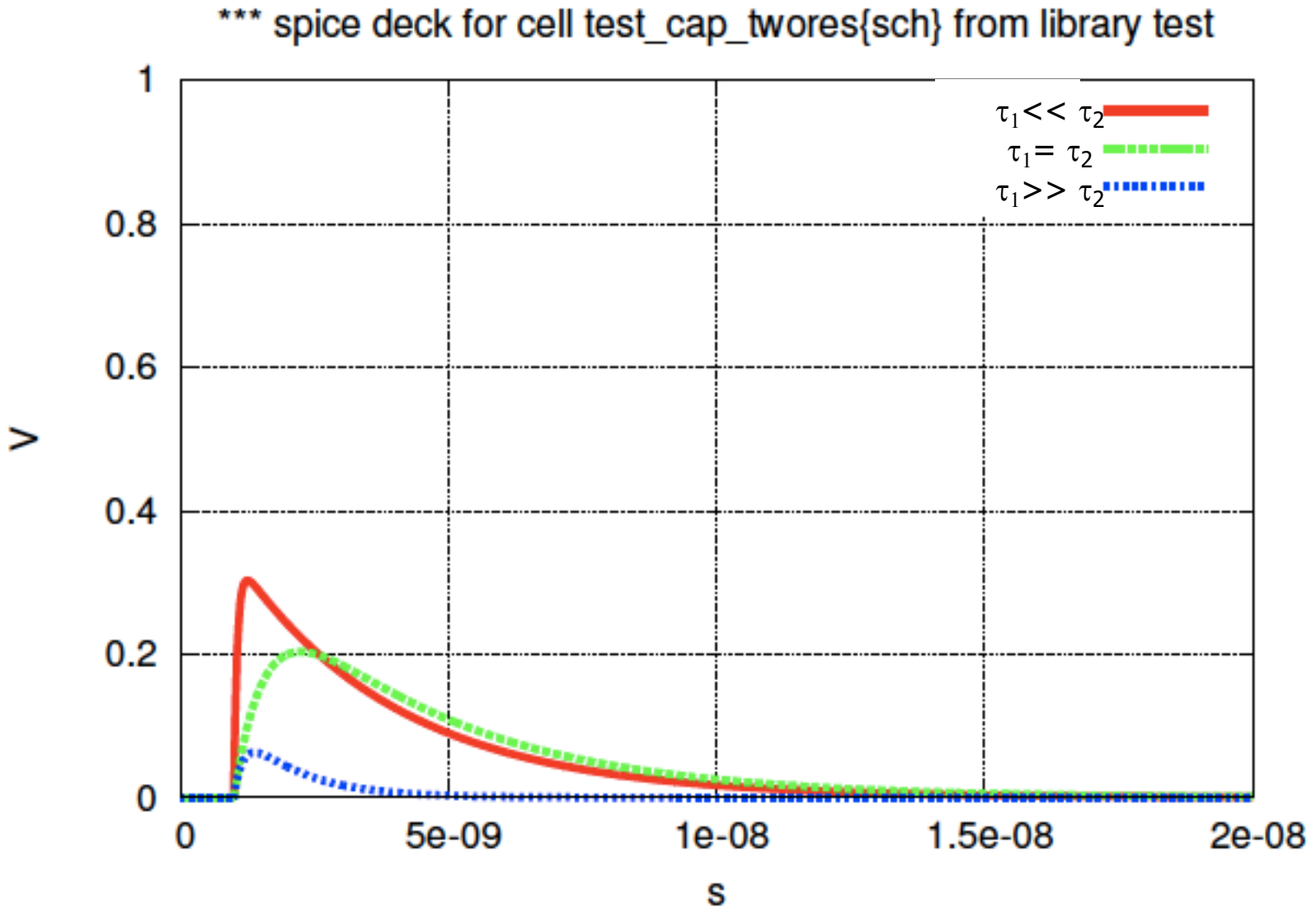
Magnitude of Noise on Driven Line

- Magnitude of diversion depends on relative time constants
 - $\tau_1 \ll \tau_2$
 - full diversion, then recover
 - $\tau_1 \gg \tau_2$
 - Drive capacitor (C_2) faster than line 1 can change
 - little noise
 - $\tau_1 \sim \tau_2$
 - Somewhere in between



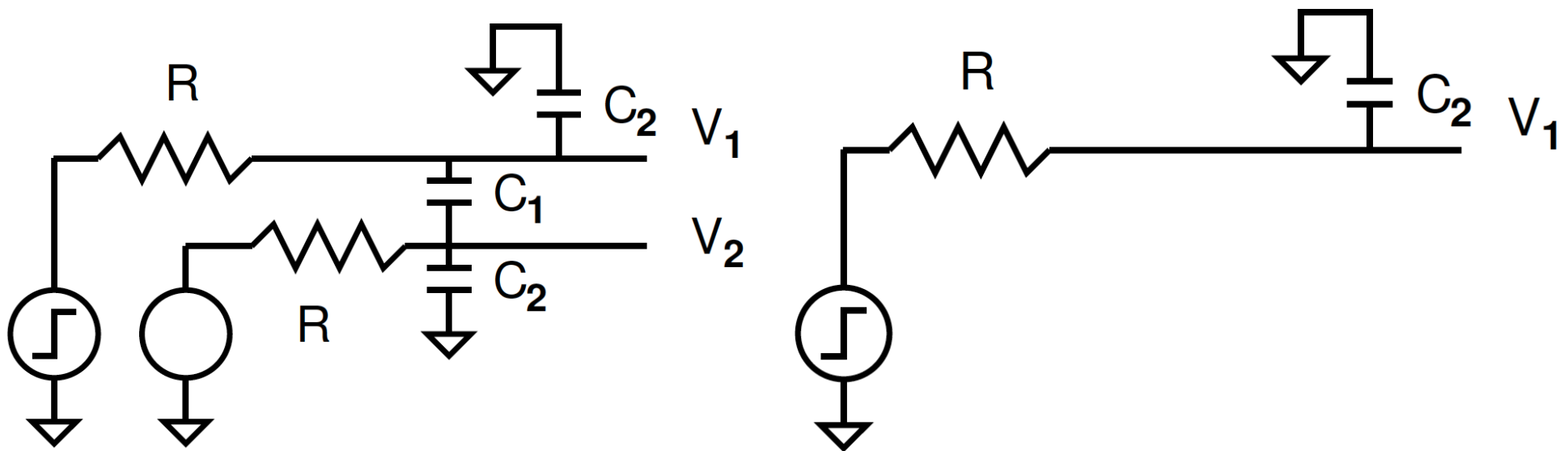


Spice: $C_1=1\text{pF}$, $C_2=2\text{pF}$



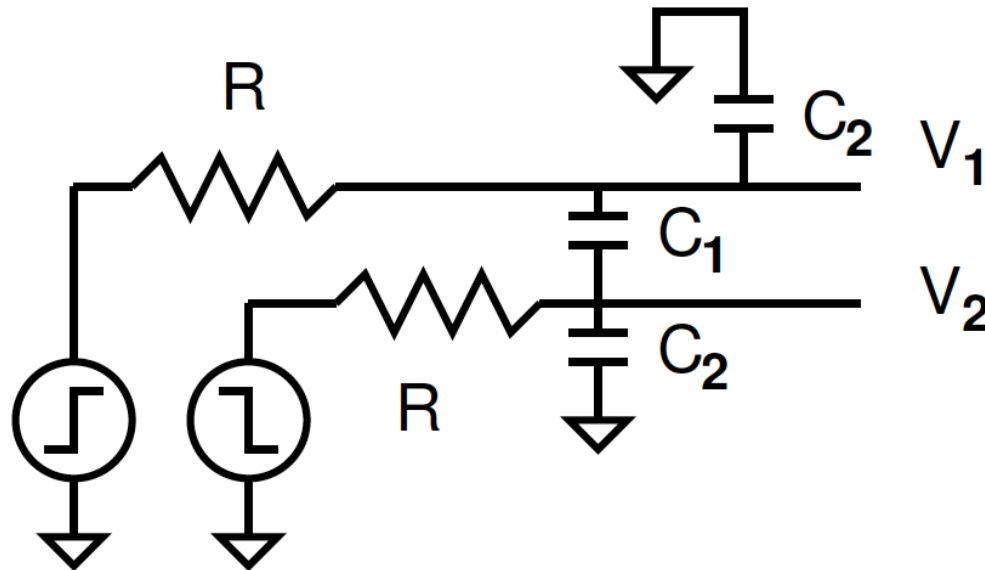
Switching Line with Finite Drive

- What impact does the presence of the neighbour line have on the **switching** line?
 - All previous questions were about noise on non-switching wire
 - Finite drive (R)



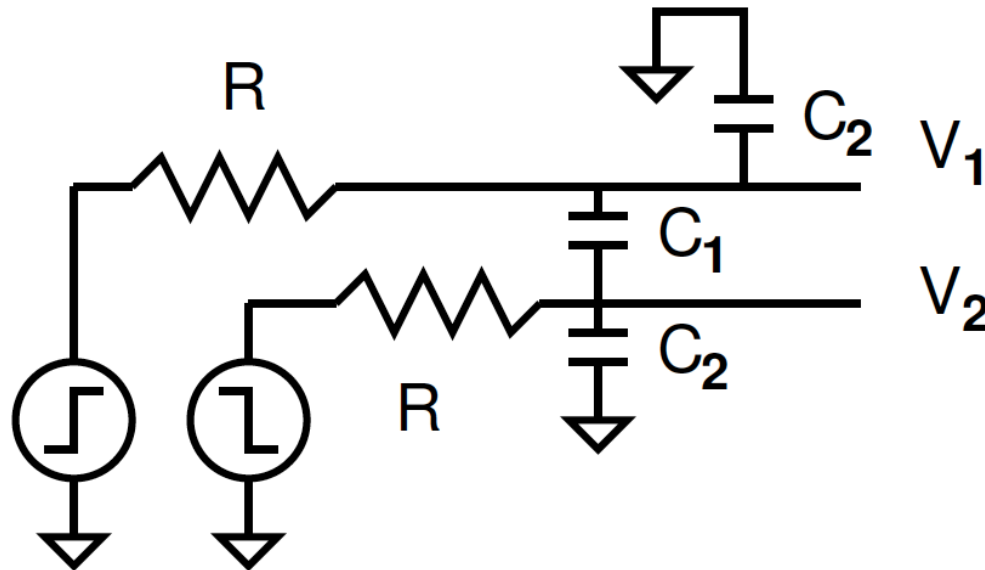
Simultaneous Transition

- What happens if lines transition in opposite directions?



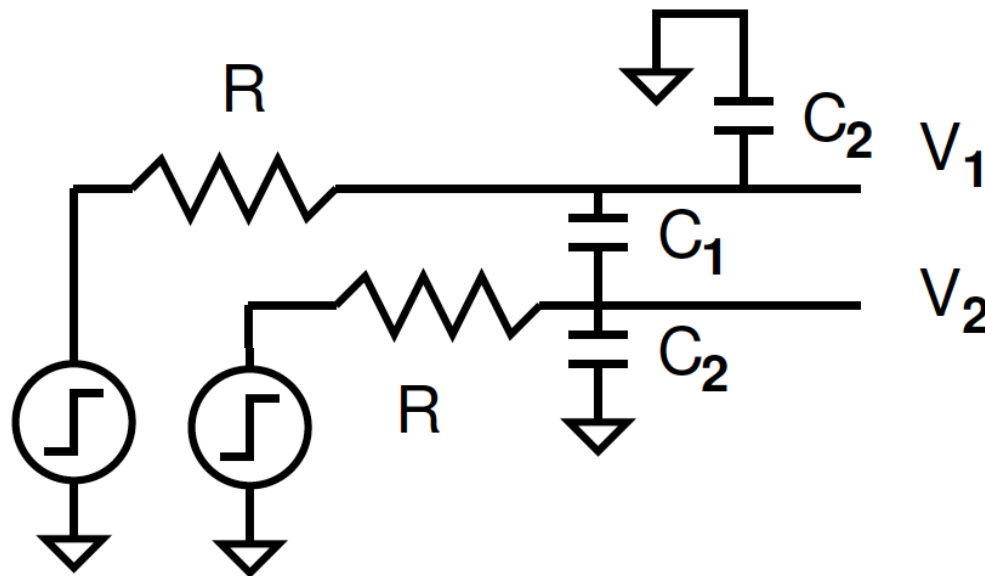
Simultaneous Transition

- What happens if lines transition in opposite directions?
 - Must charge C_1 by $2V$
 - Or looks like $2C_1$ between wires



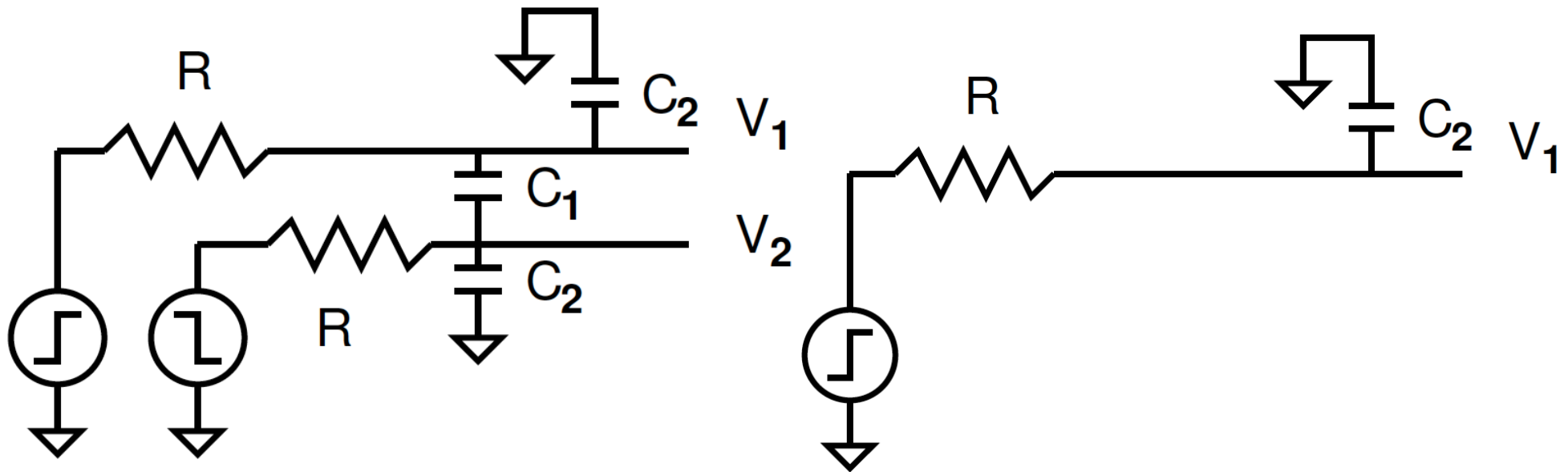
Simultaneous Transition

- What happens if lines transition in same direction?

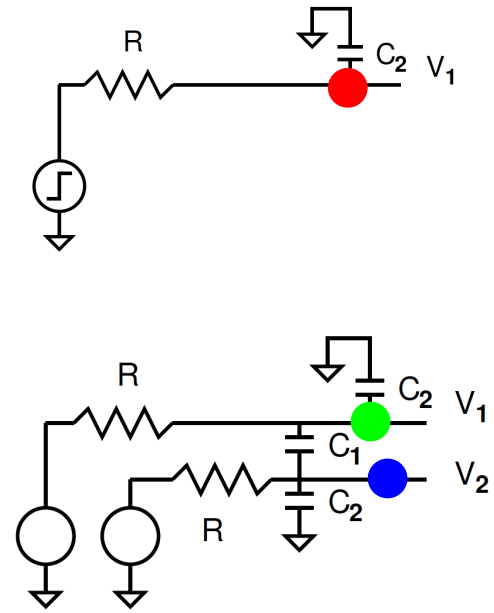
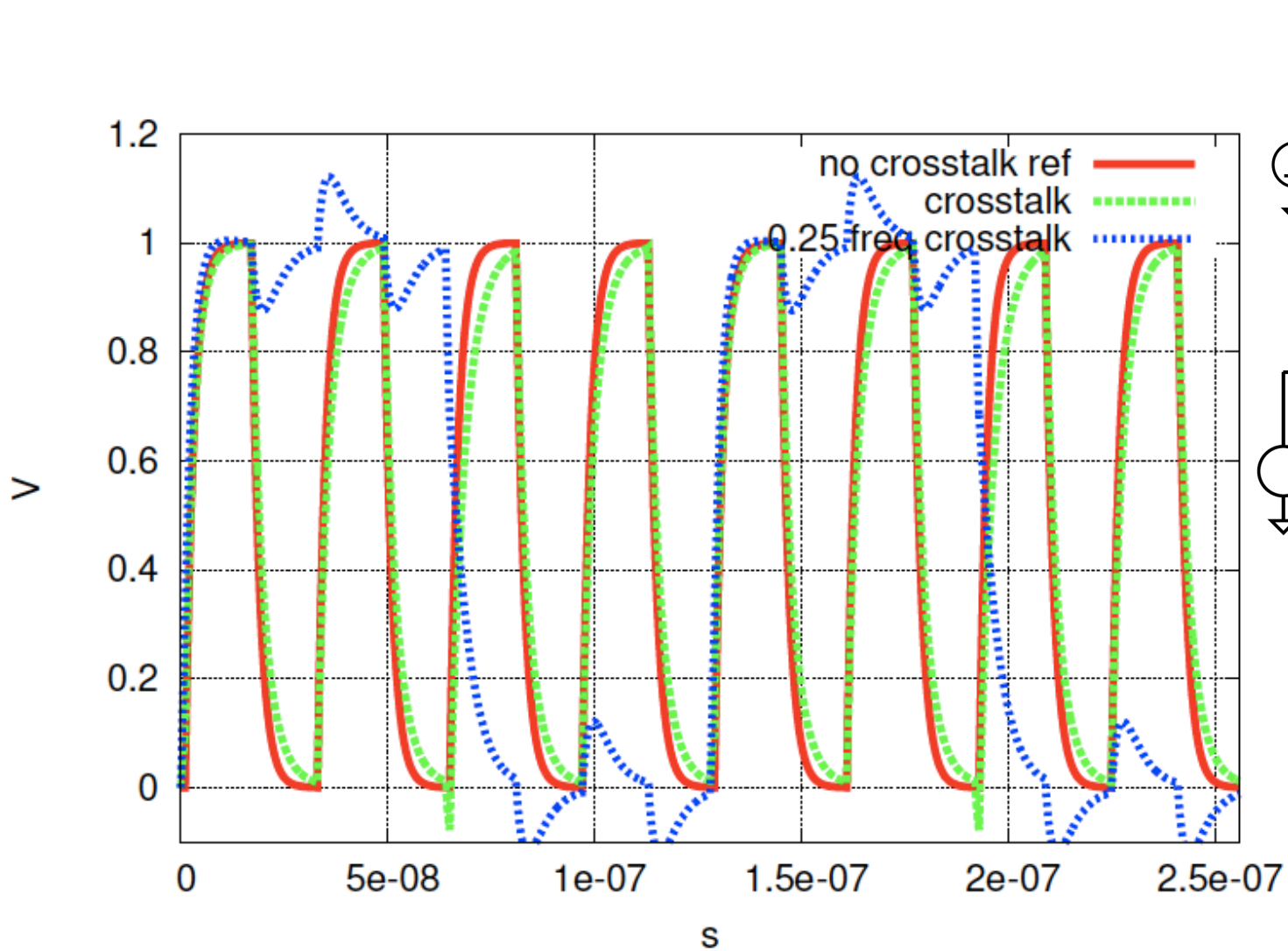


Simulation

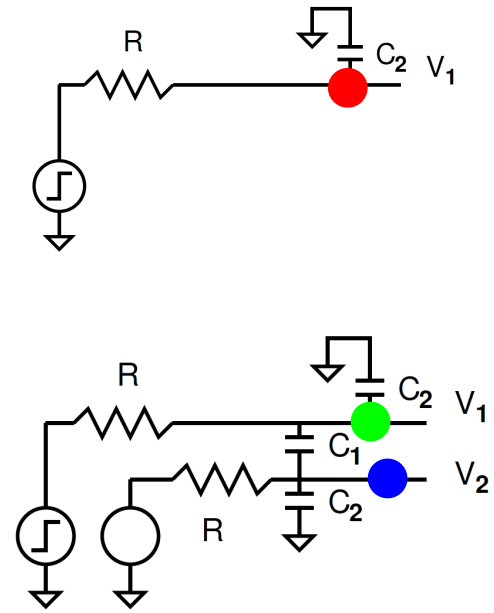
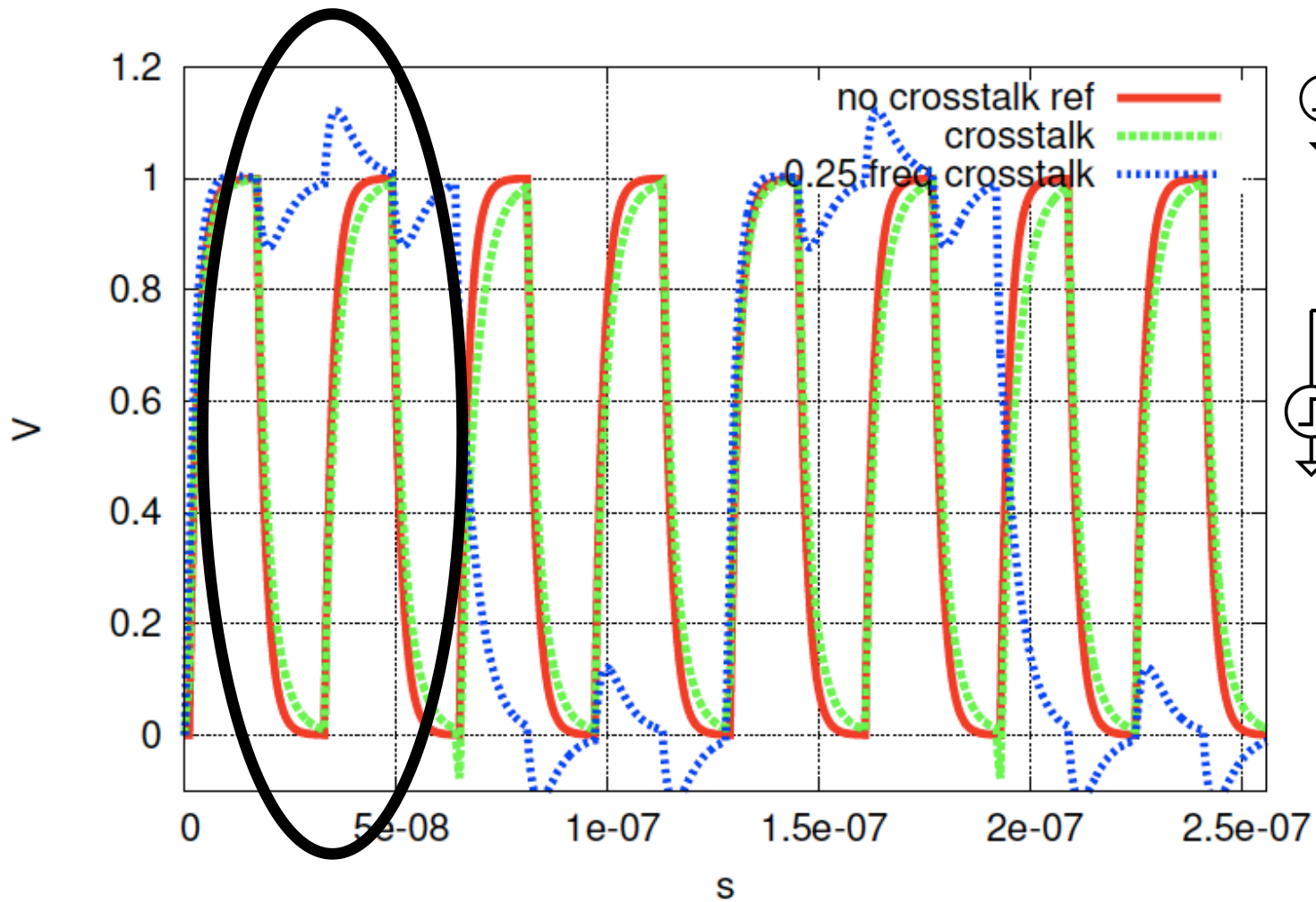
- ❑ V_2 switching at $1/4$ frequency of V_1
- ❑ No crosstalk reference case where no V_2



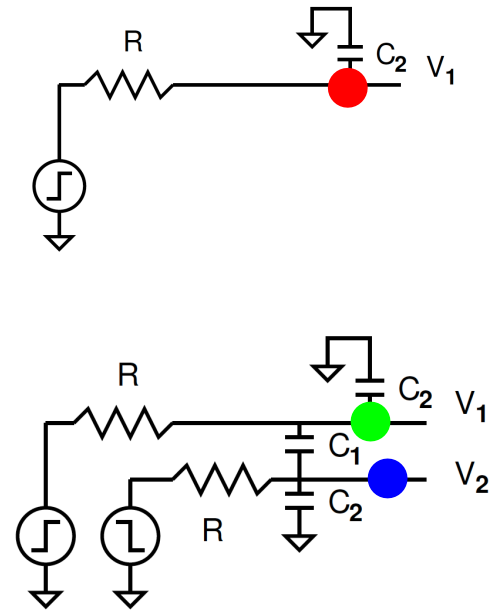
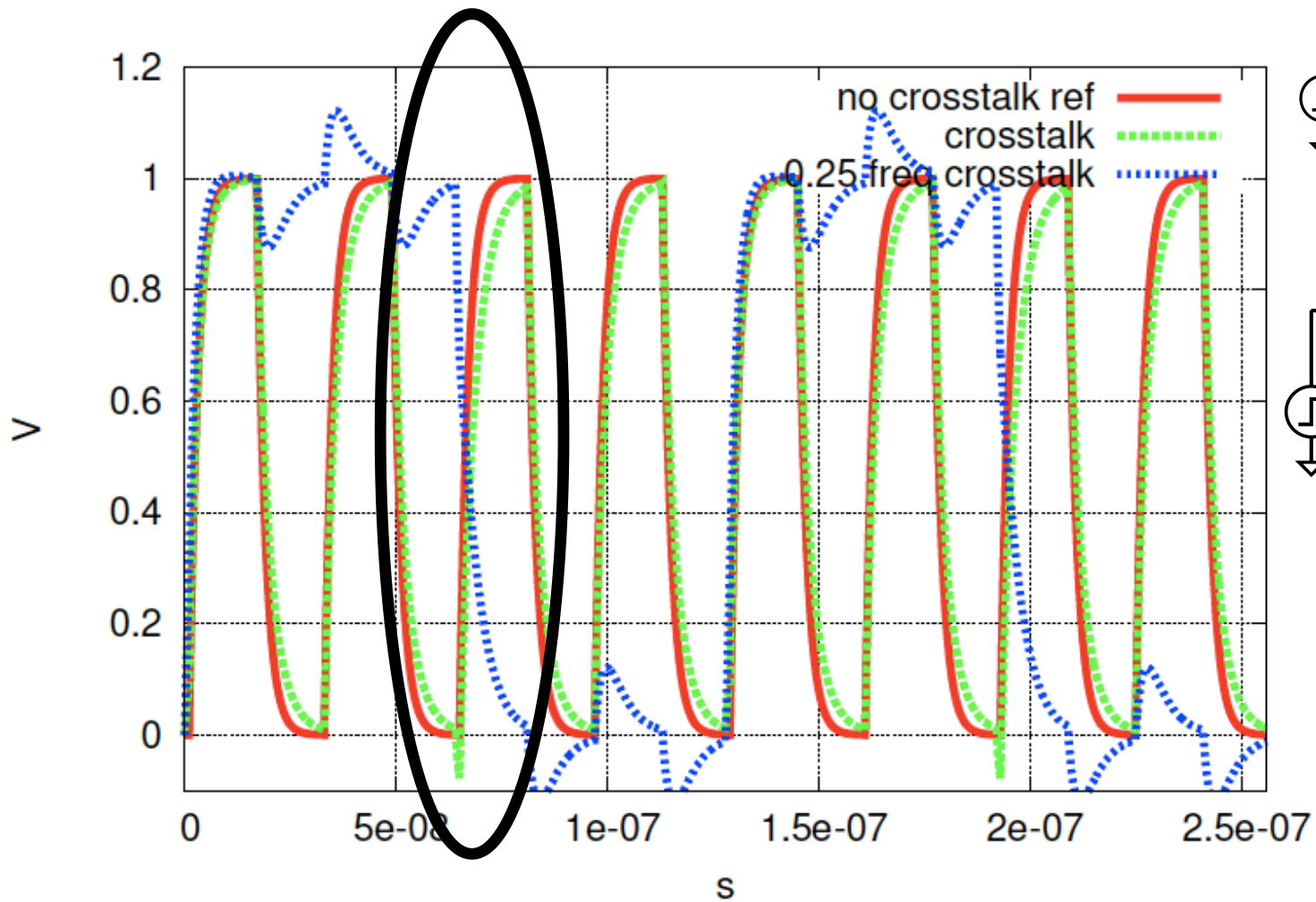
Crosstalk Neighbor Simulations



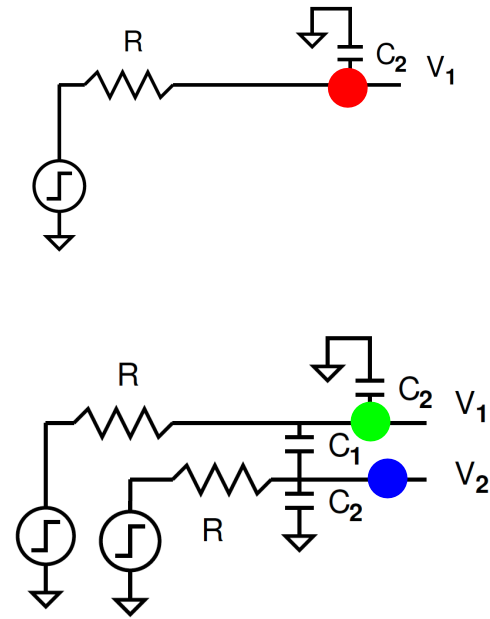
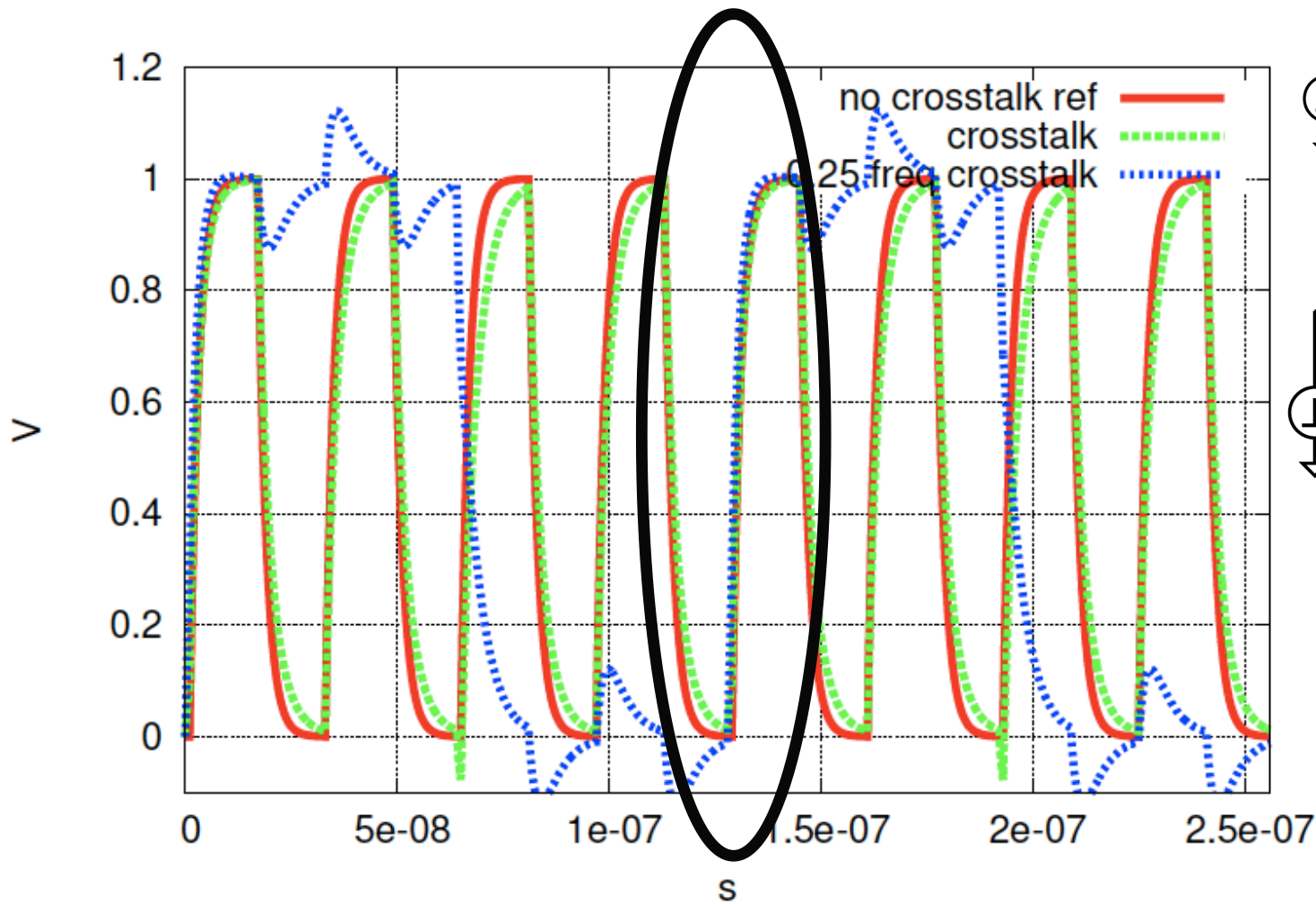
Crosstalk Neighbor Simulations



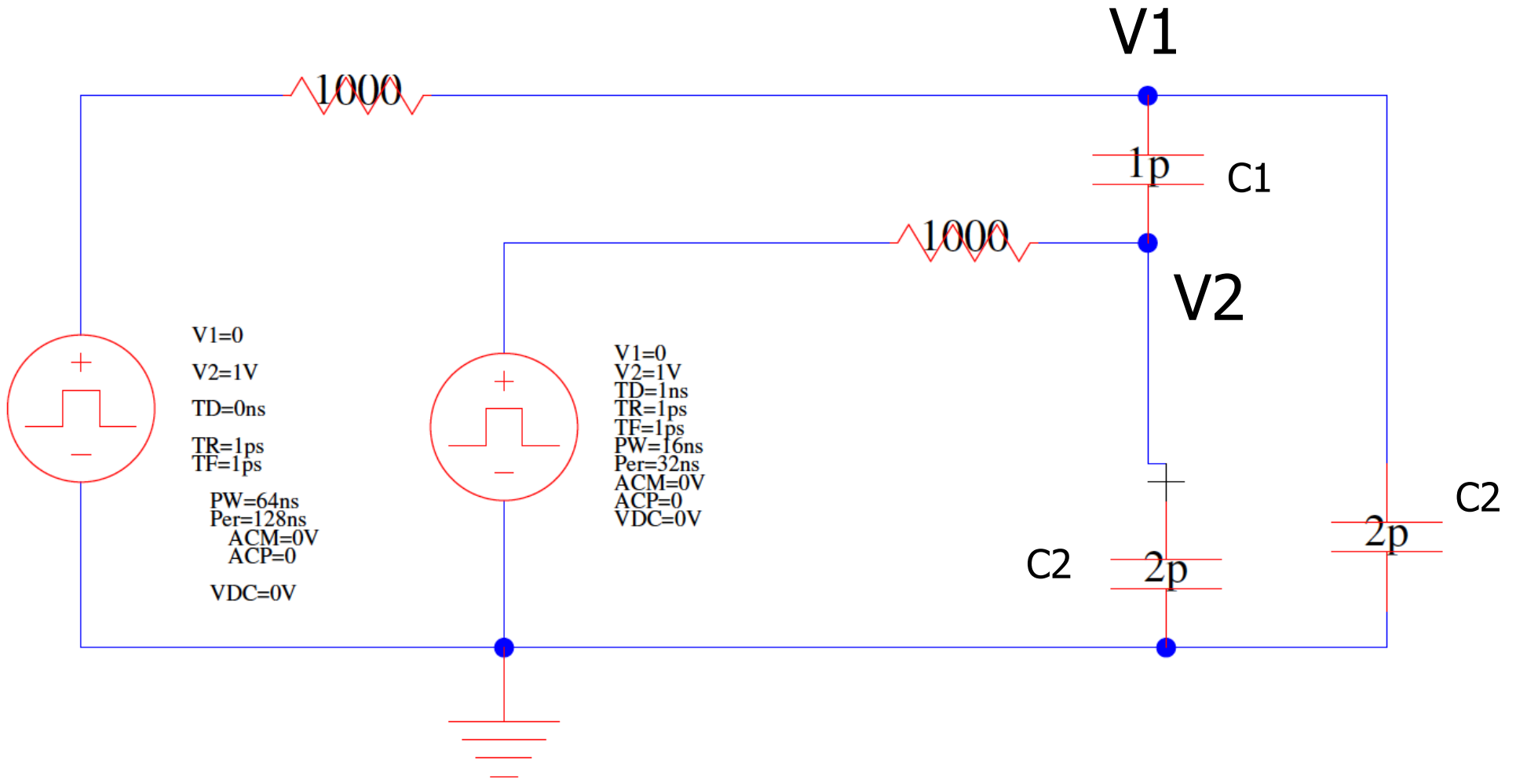
Crosstalk Neighbor Simulations



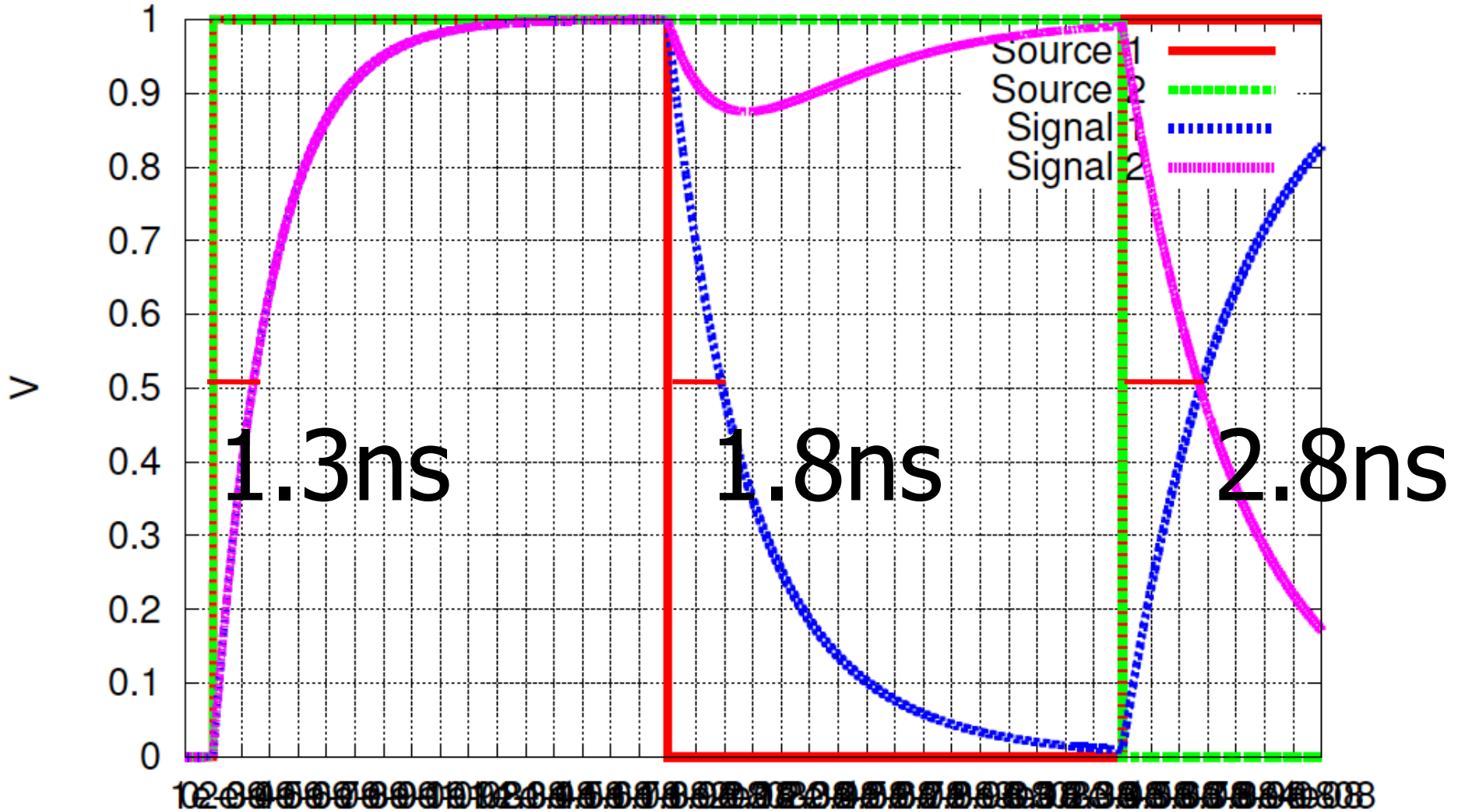
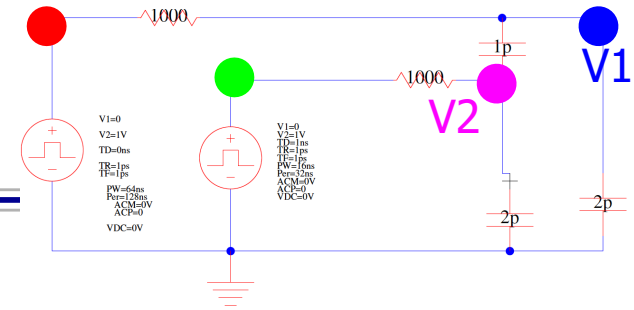
Crosstalk Neighbor Simulations



Simulation Setup



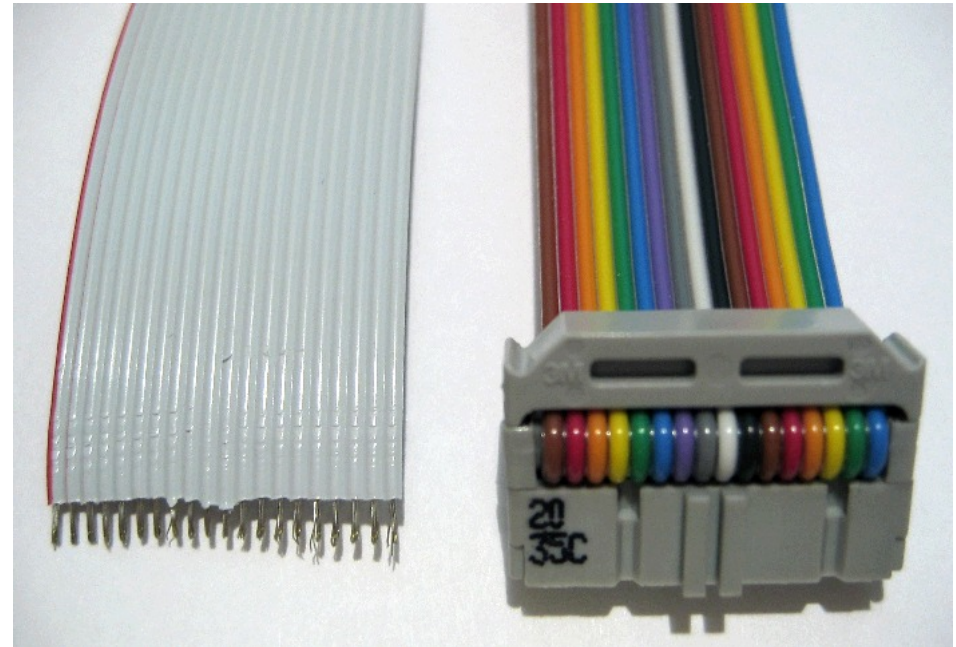
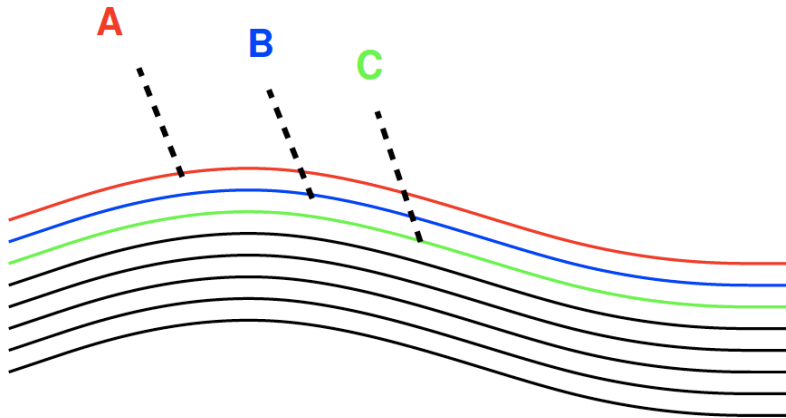
Crosstalk Simulation



Where Does it Arise?

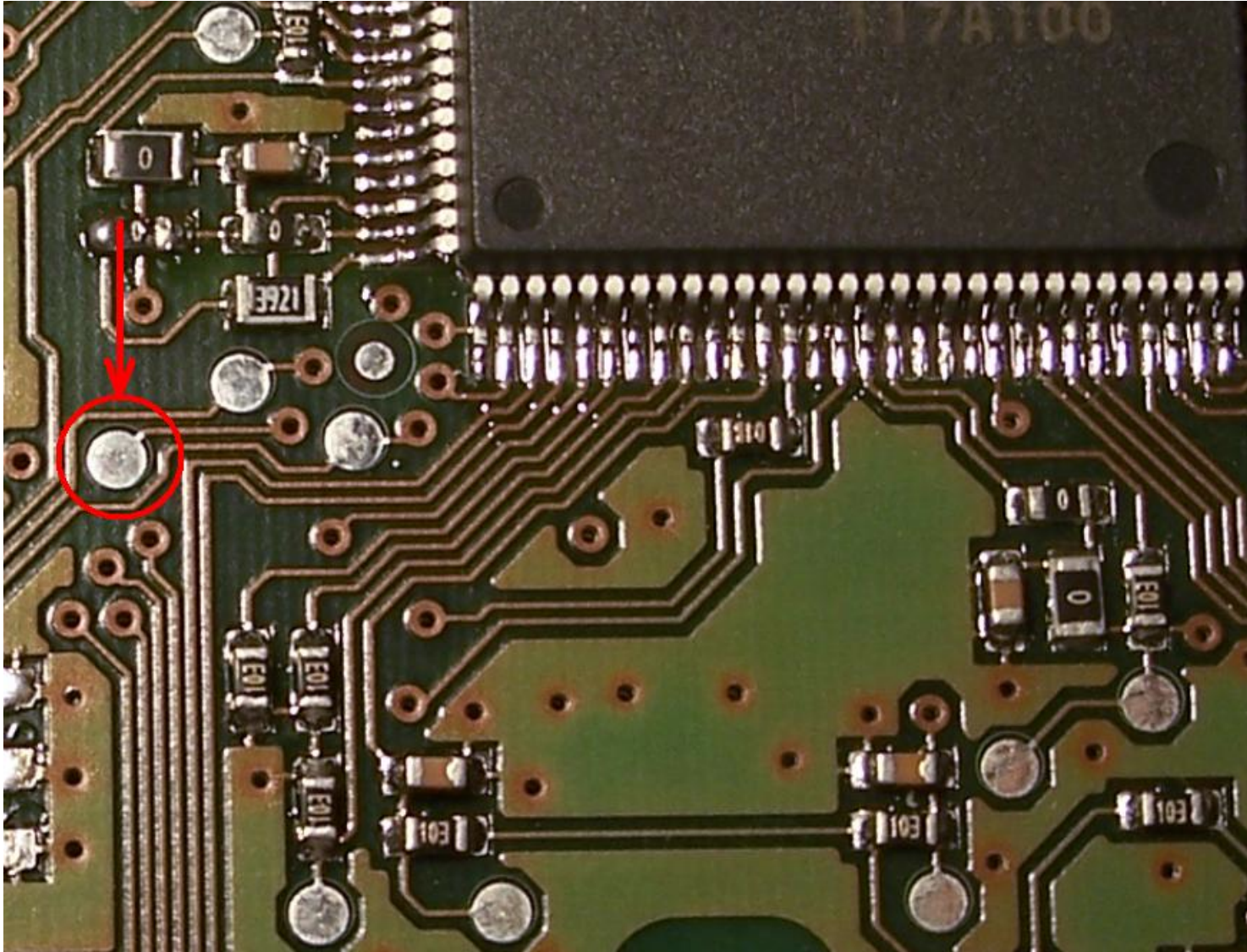


Cables and PCB Wires



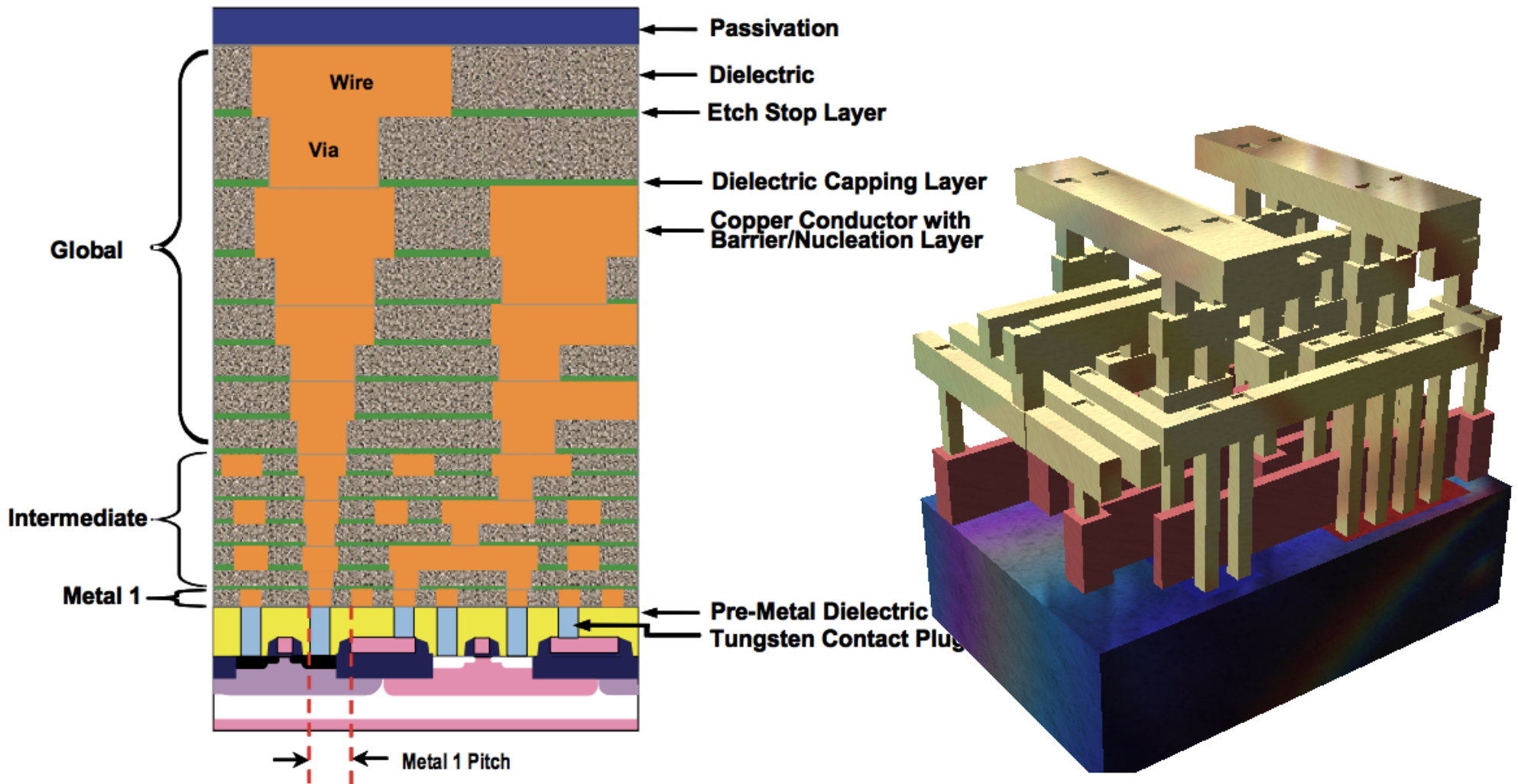
Source; <http://en.wikipedia.org/wiki/File:Flachbandkabel.jpg>

Printed Circuit Board

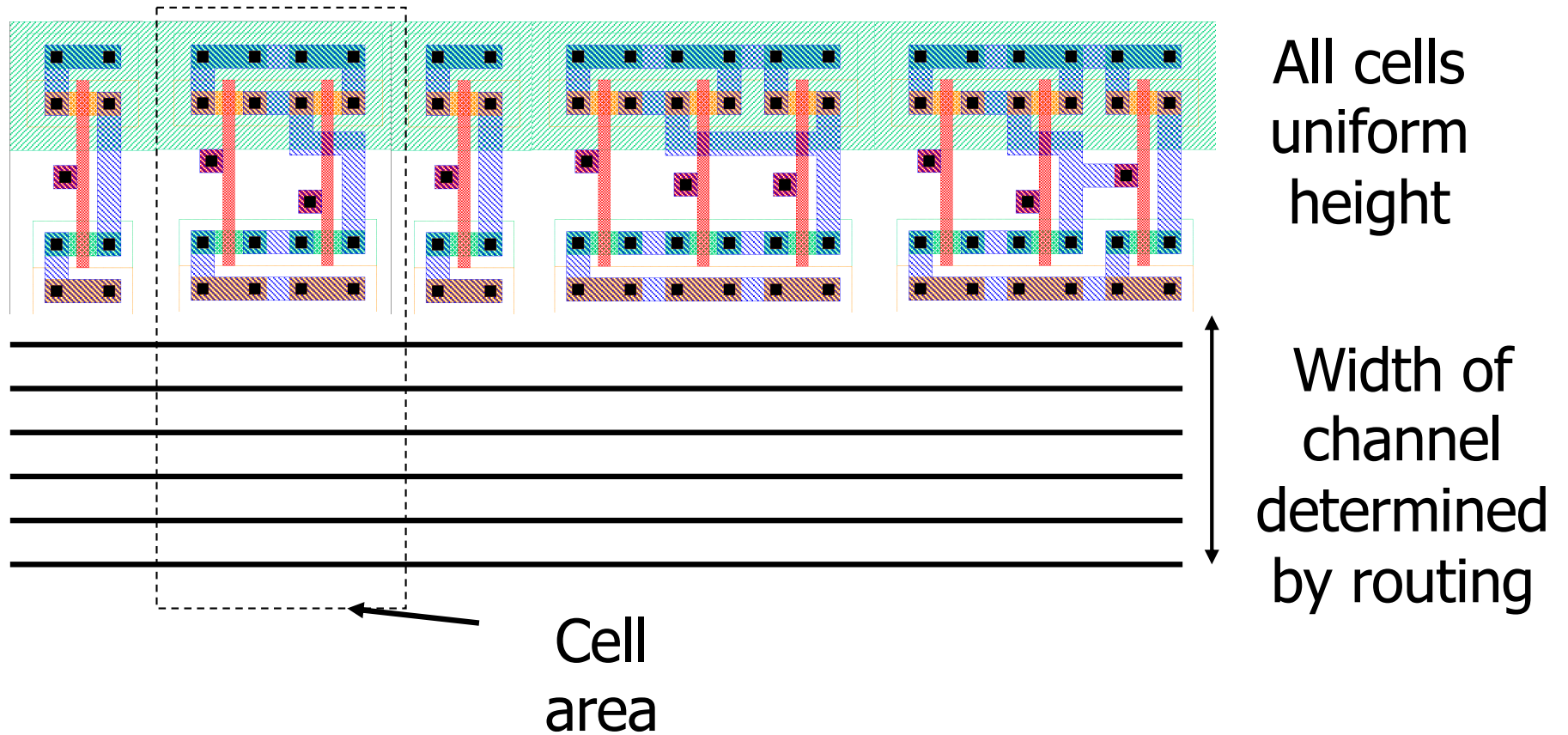


Source: <http://en.wikipedia.org/wiki/File:Testpad.JPG>

Interconnect Cross Section



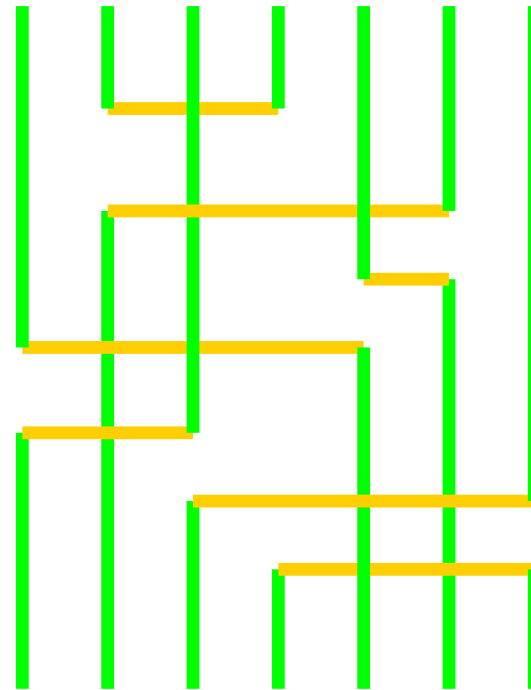
Standard Cell Area





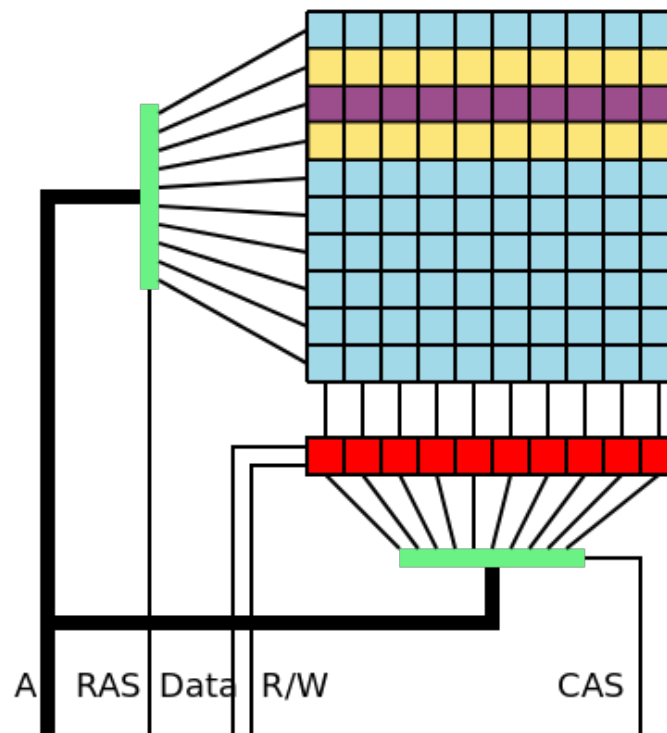
Wires

- Will be capacitively coupled to many adjacent wires of varying degrees



Rowhammer Attack

- ❑ Smaller and higher density DRAMs leads to increase electromagnetic interactions between memory cells
- ❑ Rapid wordline switching can affect adjacent words causing them to flip





Noise Implications

- ❑ *So what* if we have noise?
- ❑ If the noise is less than the noise margin, nothing happens
- ❑ Static CMOS logic will eventually settle to correct output even if disturbed by large noise spikes
 - But glitches cause extra delay
 - Also cause extra power from false transitions
- ❑ Dynamic logic never recovers from glitches
 - Can't correct mid-cycle, need precharge nodes
- ❑ Memories and other sensitive circuits also can produce the wrong result



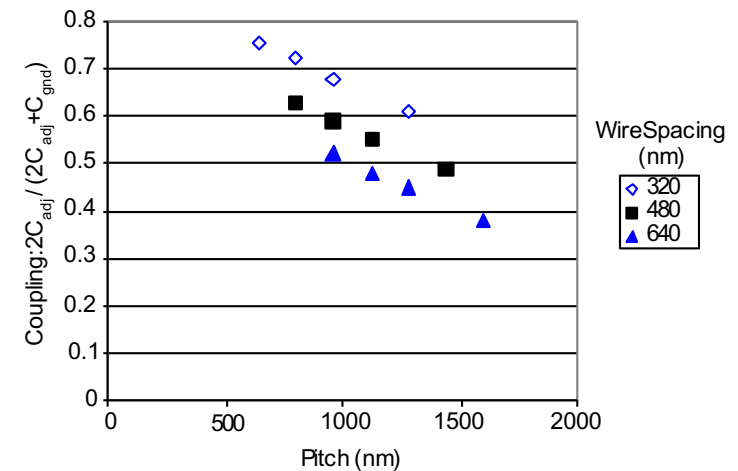
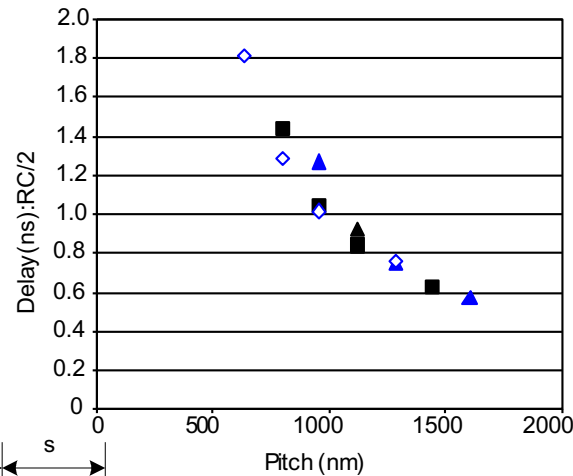
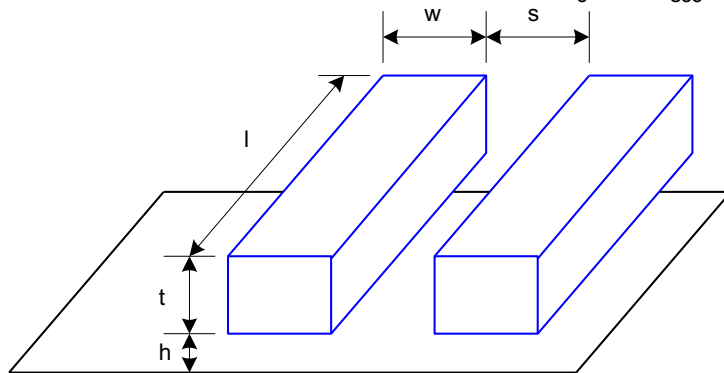
Wire Engineering

- ❑ Goal: achieve delay, area, power goals with acceptable noise
- ❑ Degrees of freedom:

Wire Engineering

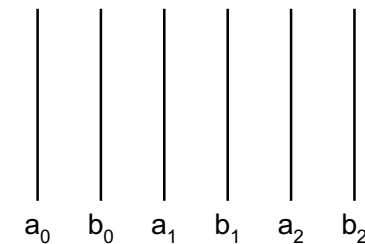
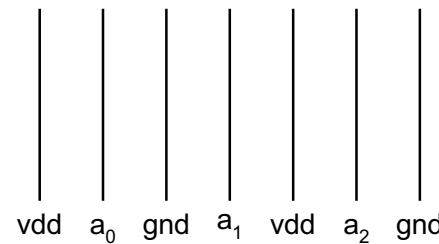
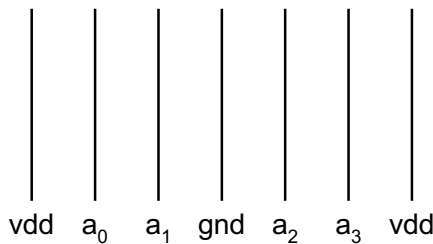
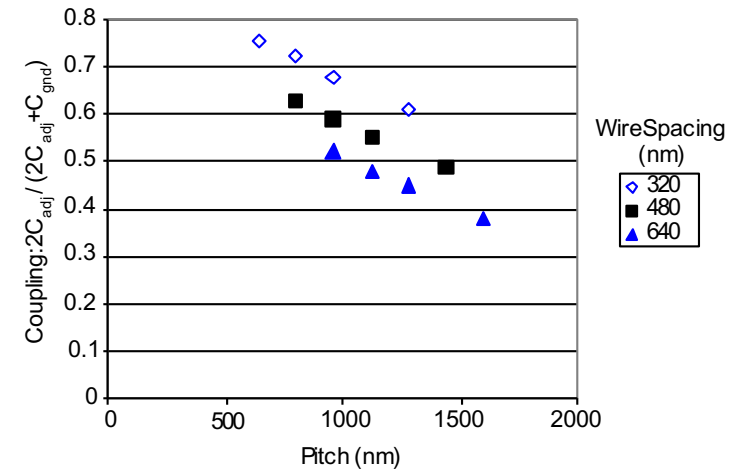
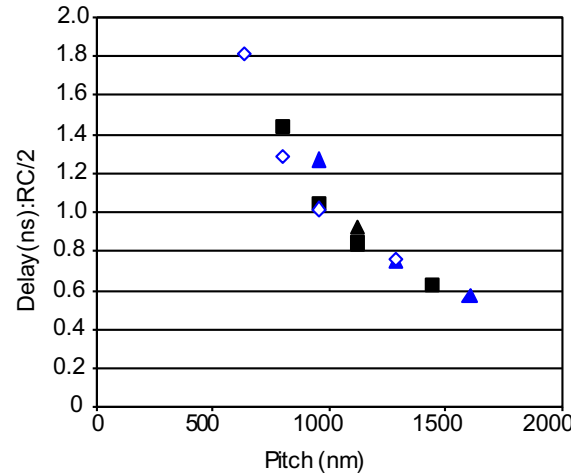
- ❑ Goal: achieve delay, area, power goals with acceptable noise
- ❑ Degrees of freedom:

- Width
- Spacing
- Layer



Wire Engineering

- ❑ Goal: achieve delay, area, power goals with acceptable noise
- ❑ Degrees of freedom:
 - Width
 - Spacing
 - Layer
 - Shielding





Idea

- ❑ Capacitance is everywhere
- ❑ Especially between adjacent wires
- ❑ Will get “noise” from crosstalk
- ❑ Clocked and driven wires
 - Slow down transitions
- ❑ Undriven wires voltage changed
- ❑ Can cause spurious transitions



Admin

- ❑ Monday 11/29 in Ketterer again, no lecture
- ❑ Project 2
 - Due Friday 12/3
 - Milestone feedback:
 - Don't forget about the clock
 - Controls registers to allow inputs to change at any time, but only affect memory at clk edge
 - Non-overlapping clocks!
 - Get SRAM column/row working first to make testing/debugging smoother
 - Can use a min size cell, just have to justify why that sizing